

Role of surface oxide and anodization in Nb₃Sn nucleation

Liana Shpani¹, Jasper Brown², Van Do², Gabriel Gaitan¹, Matthias Liepe¹, Steven Sibener²

¹Cornell University, Ithaca, NY, USA ²University of Chicago, Chicago, IL, USA

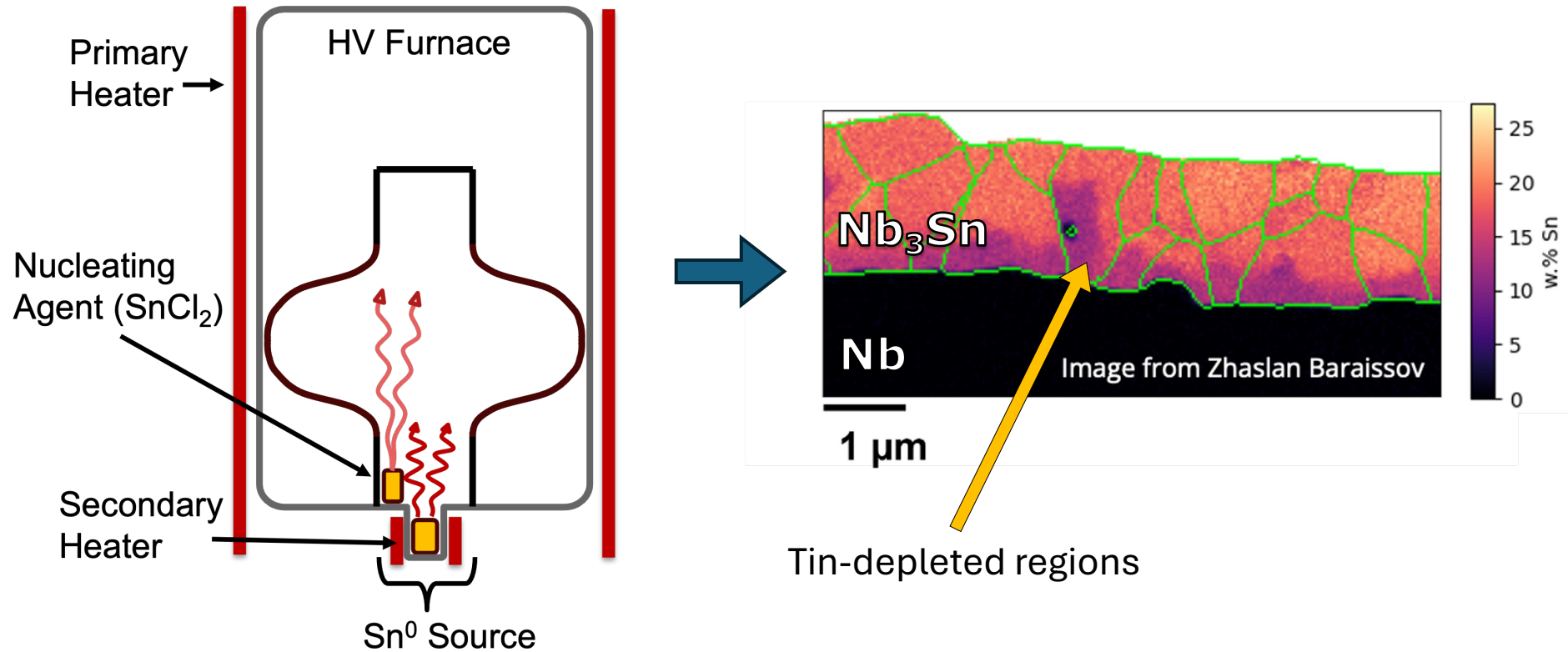
Research funded by Center for Bright Beams, NSF award PHY-1549132. Work also supported by U.S. DOE Office of High Energy Physics under grant No. DE-SC0008431. This work made use of the Cornell Center for Materials Research shared instrumentation facility.



Cornell University



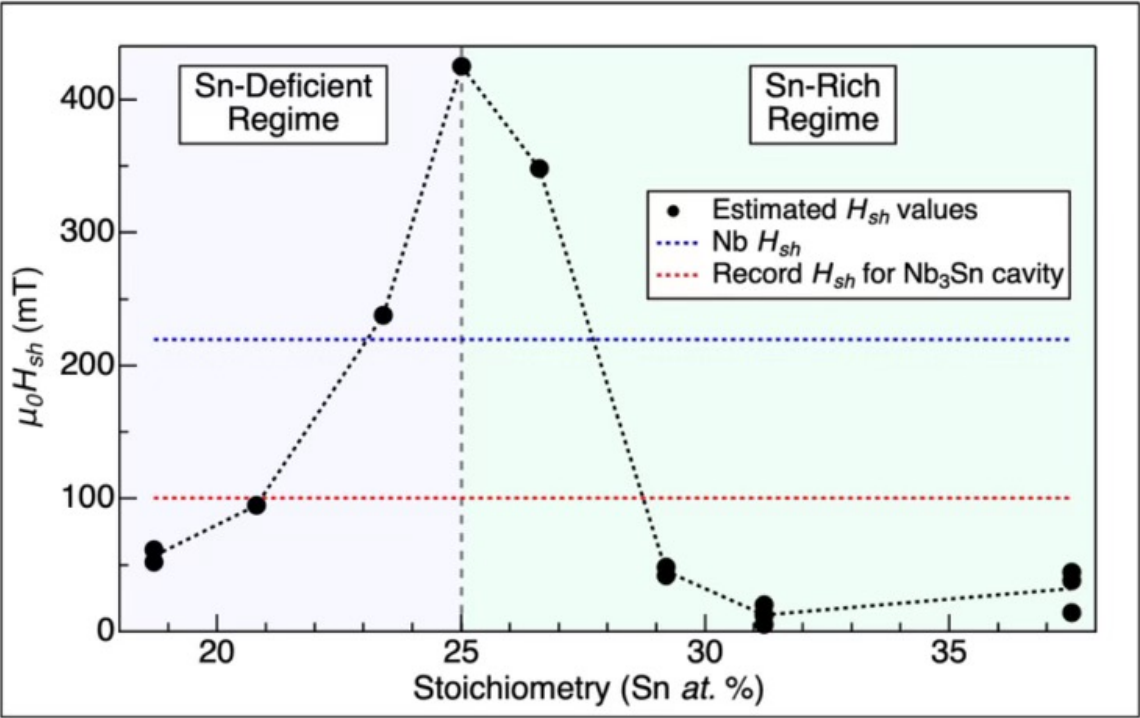
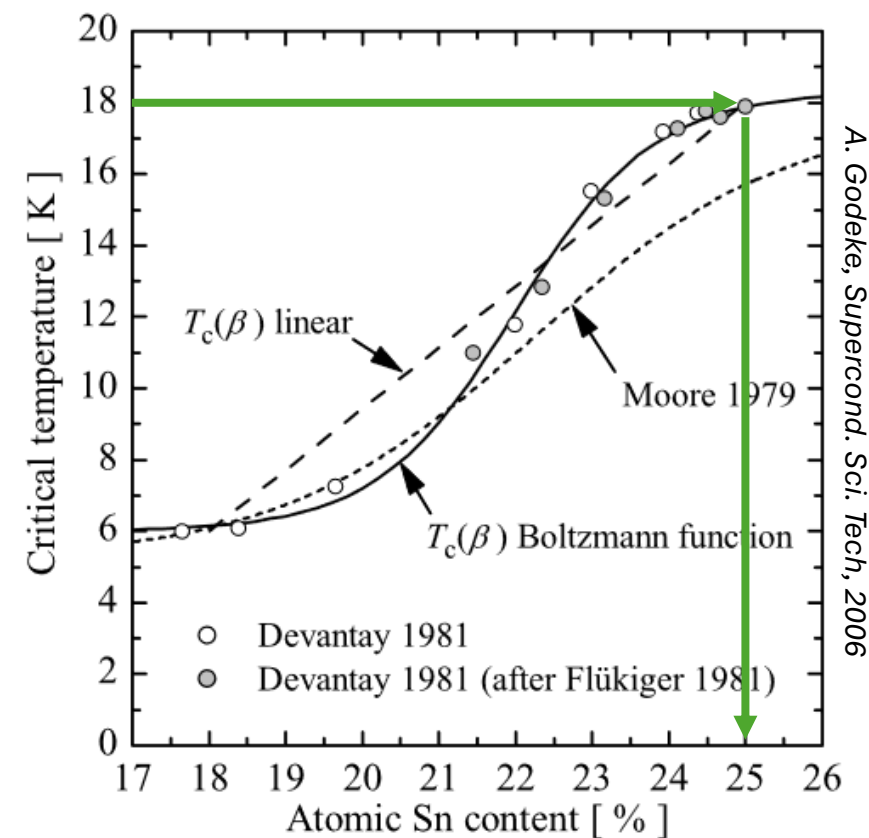
How Nb₃Sn is made and where it falls short



S. Posen and M. Liepe, Phys. Rev. ST Accel. Beams 15, 112001 (2014)

Vapor-diffusion growth leaves tin-depleted regions throughout the film

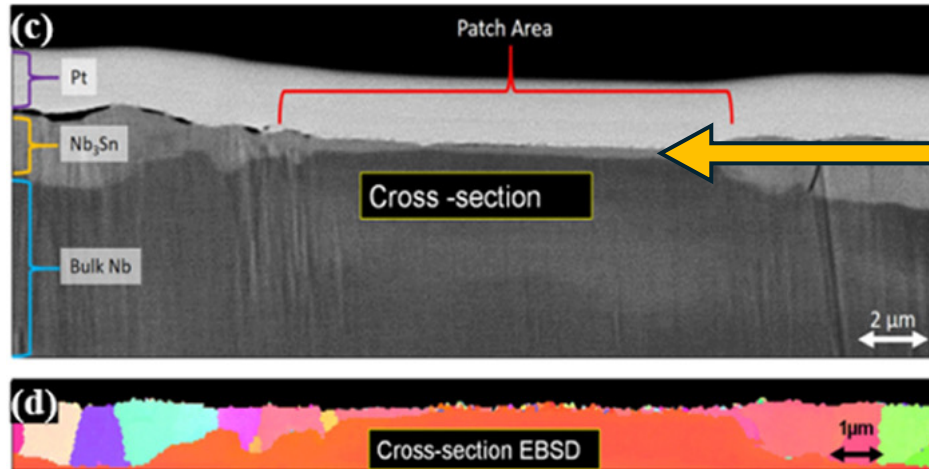
Small stoichiometry deviations, big performance loss



Willson, Harbick et al. 2024 Phys. Rev. Res. 6 043133
DOI 10.1103/PhysRevResearch.6.043133

This tight tolerance is why good growth matters

Nucleation challenge



Large, thin tin-depleted Nb₃Sn grains

→ Once formed, very hard to 'fill in' (less grain boundaries to assist Sn diffusion)

*Pudasaini et al. 2019 J. Vac. Sci. Technol. A 37 051509
DOI 10.1116/1.5113597*

Film quality is limited by non-uniform nucleation in early stages

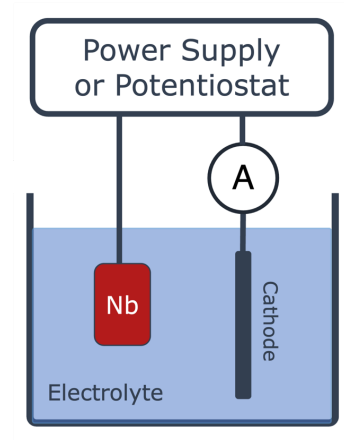
How can we improve tin nucleation?



Pre-anodization of the substrate

→ Electrochemically growing an oxide on the Nb substrate

This has been found to help with Sn nucleation since the early days of Nb₃Sn research



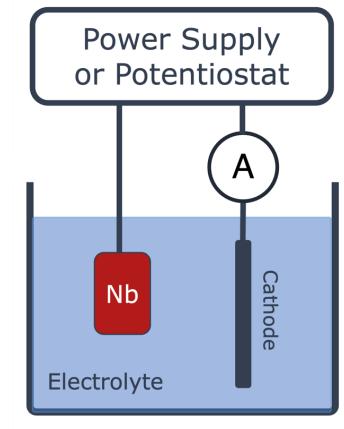
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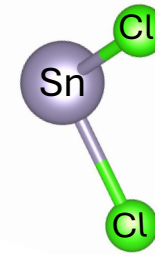
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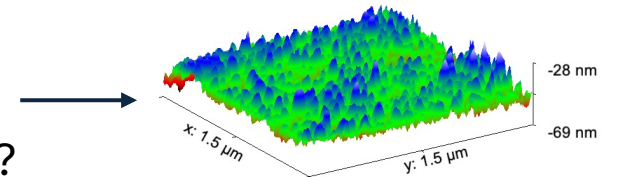
Addition of SnCl₂ nucleating agent



→ Higher vapor pressure than metallic Sn at lower temperatures

→ Interacts with the substrate surface at early stages of coating

Does SnCl₂ bind preferentially to specific features?



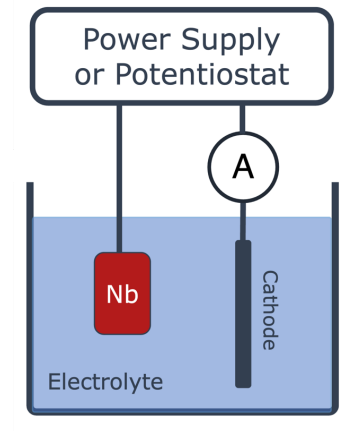
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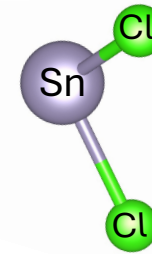
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*Sets the surface
SnCl₂ sees*



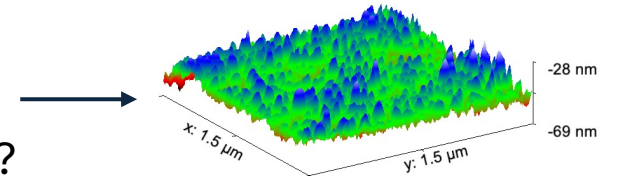
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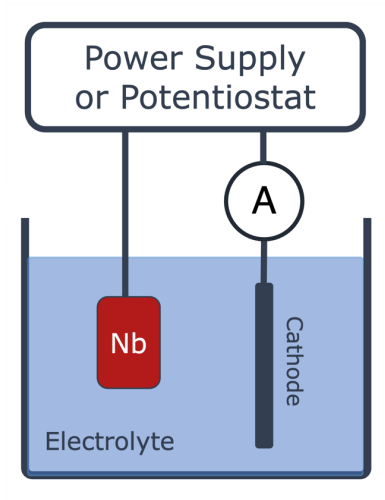
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Does SnCl₂ bind preferentially to specific features?



The oxide surface shapes early SnCl₂ nucleation

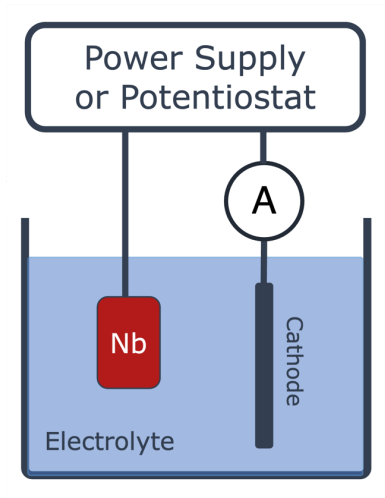
Pre-anodization, in more detail



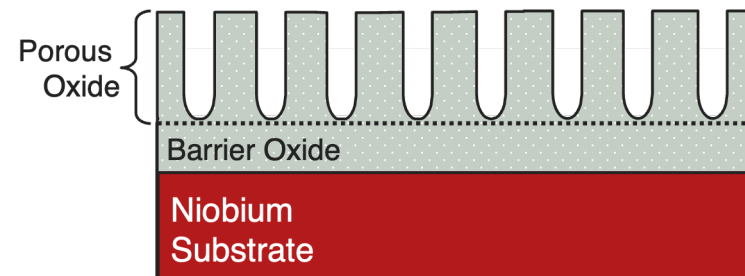
Relation often cited in SRF literature: thickness $\propto$ voltage (2-3 nm/V)

→ assumes barrier-type growth

Pre-anodization, in more detail



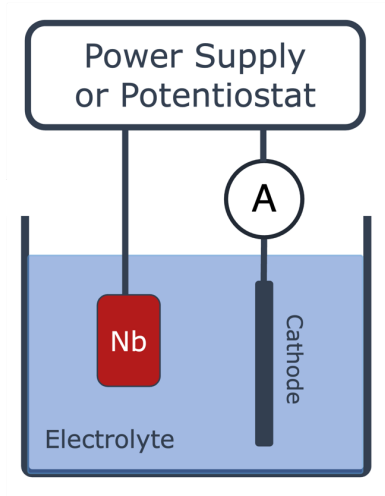
When the oxide is soluble in the electrolyte (e.g. NaOH), you can grow a porous oxide



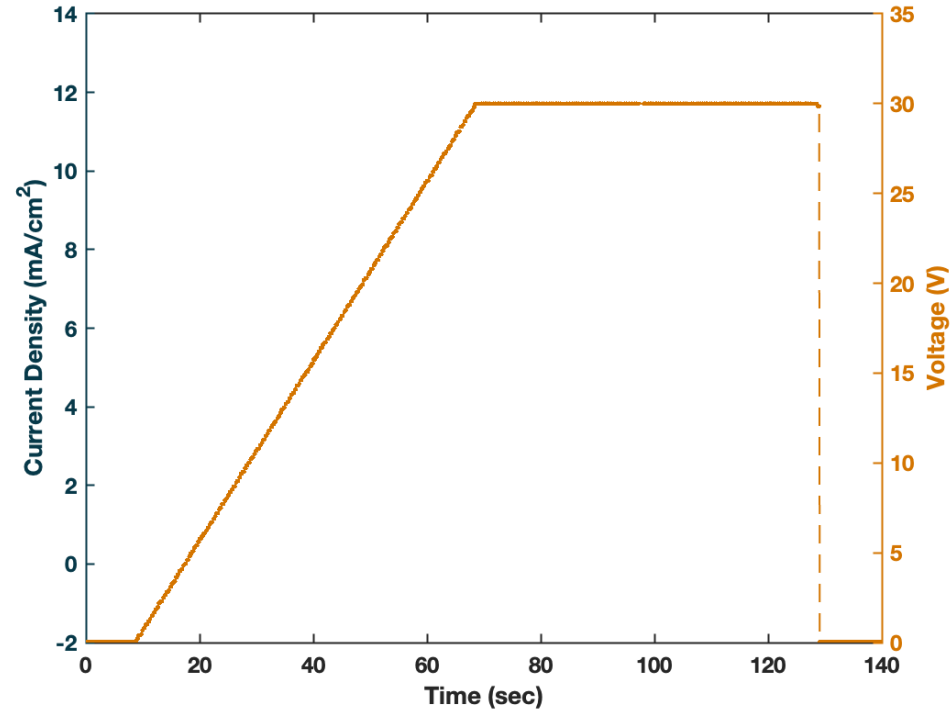
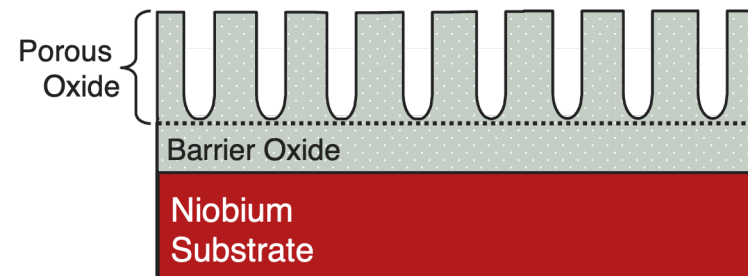
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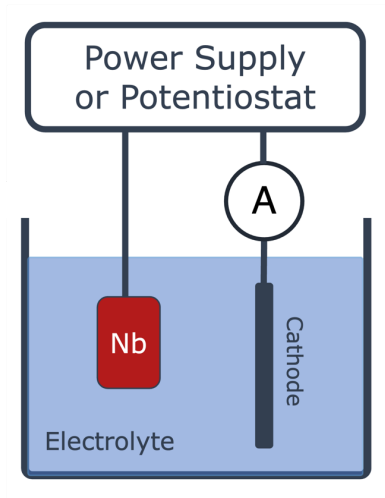
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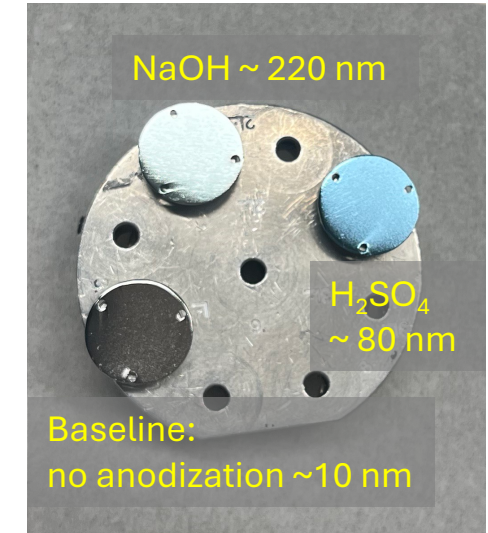
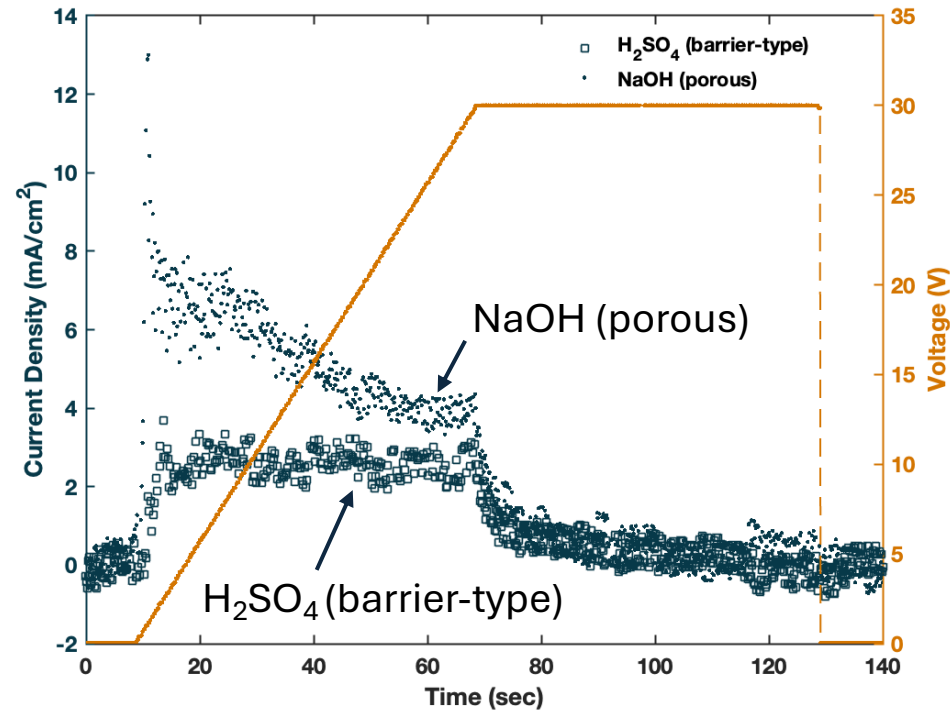
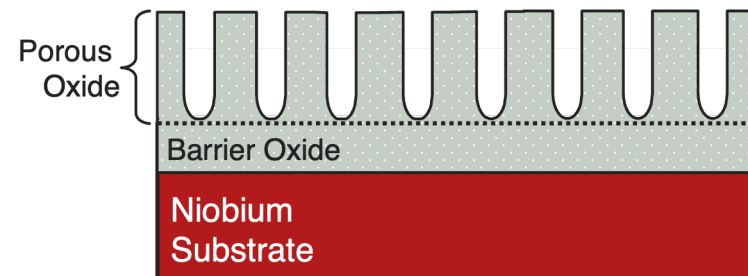
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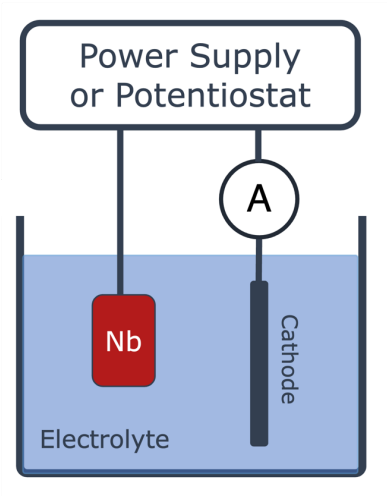
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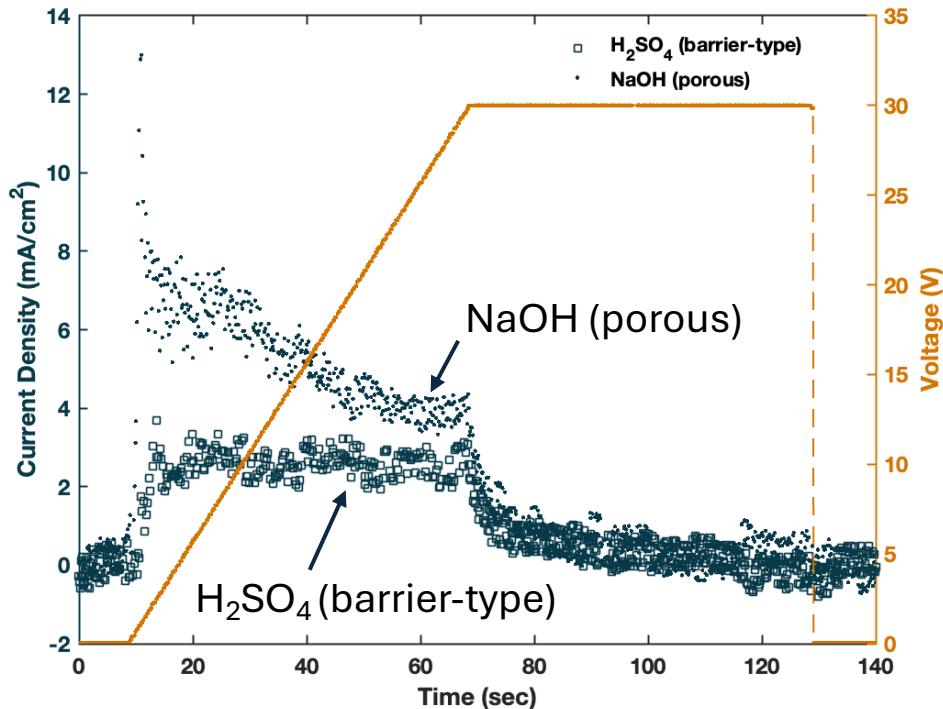
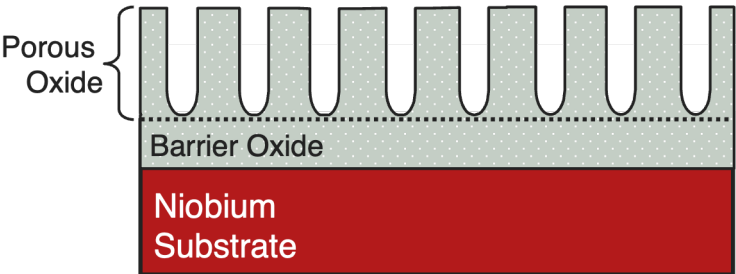
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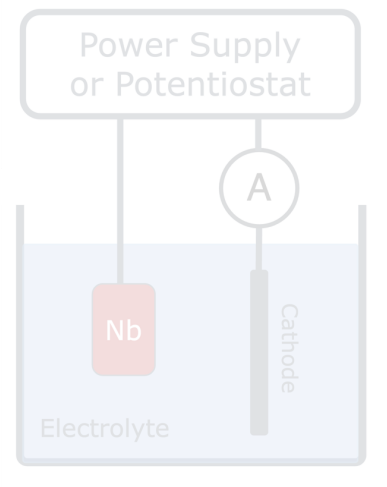


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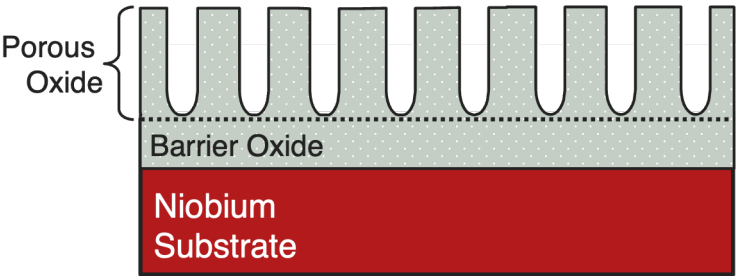
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Same voltage, different oxide: electrolyte controls morphology

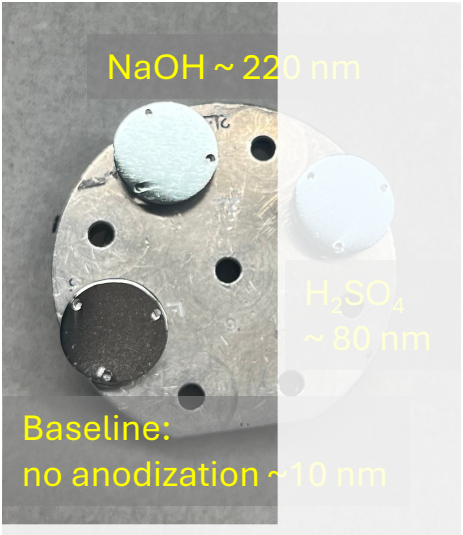
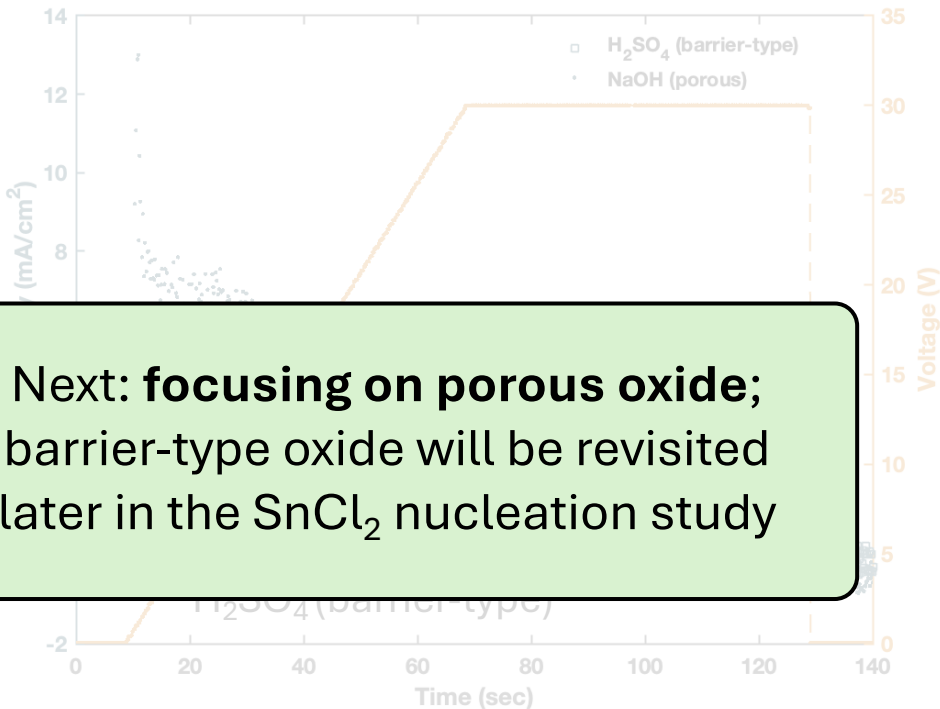
Pre-anodization, in more detail



When the oxide is soluble in the electrolyte (e.g. NaOH), you can grow a porous oxide



Next: **focusing on porous oxide**; barrier-type oxide will be revisited later in the SnCl_2 nucleation study



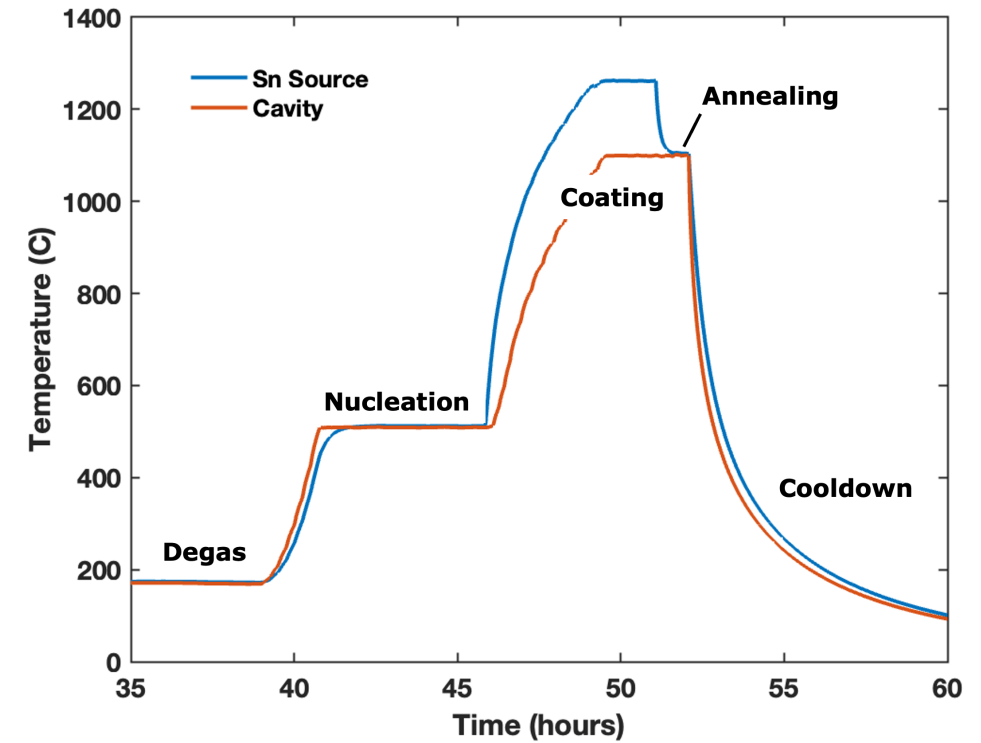
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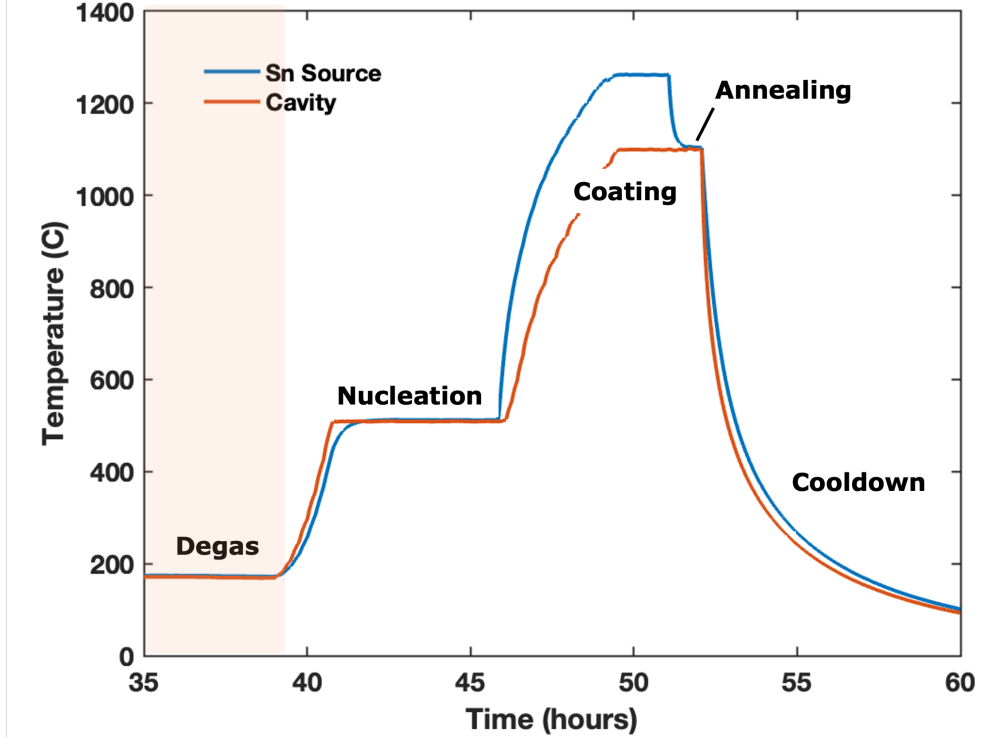
Tracking oxide evolution

Thermal vapor diffusion temperature profile



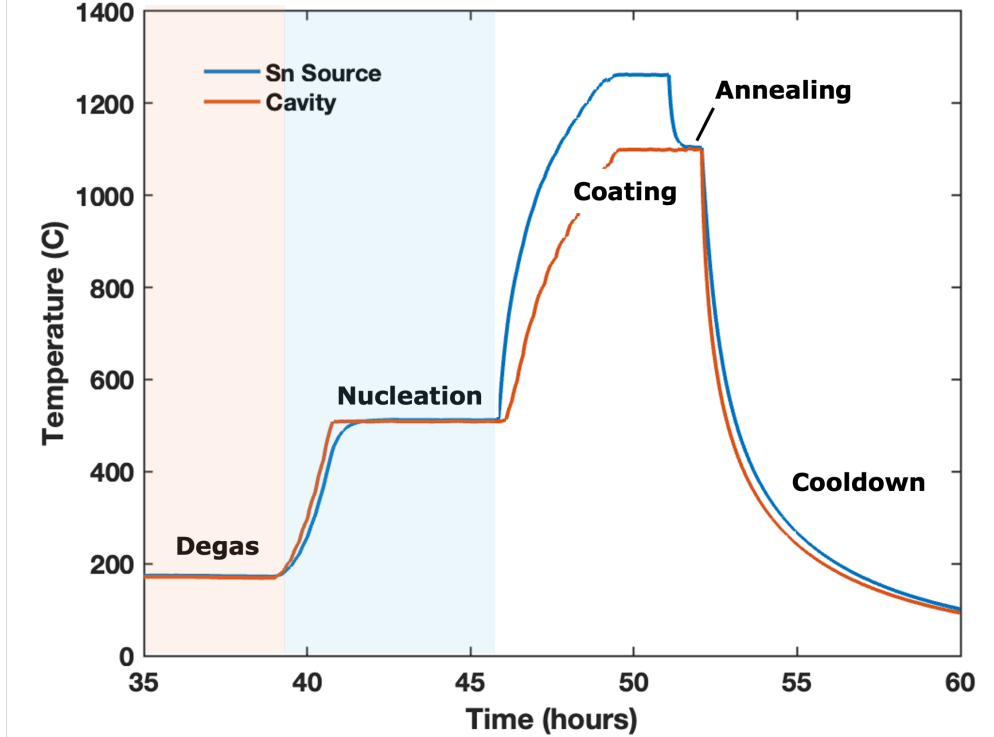
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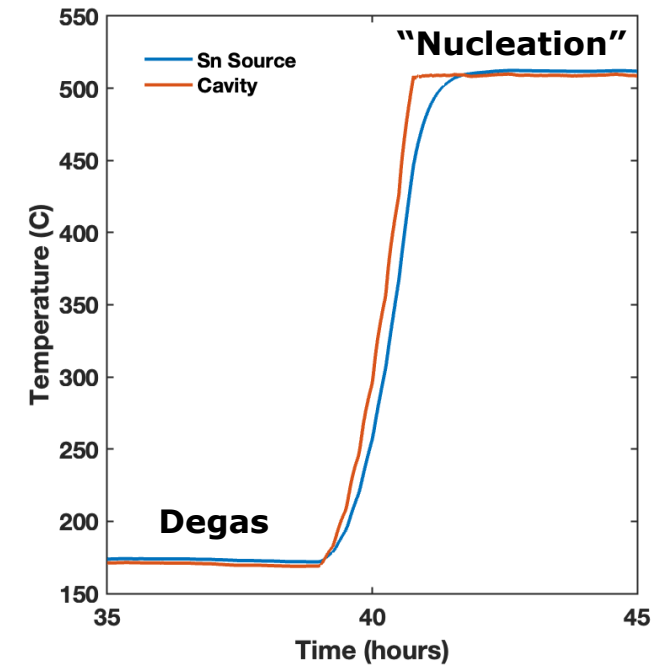


Tracking oxide evolution

Thermal vapor diffusion temperature profile



Tracking oxide evolution



Jasper Brown



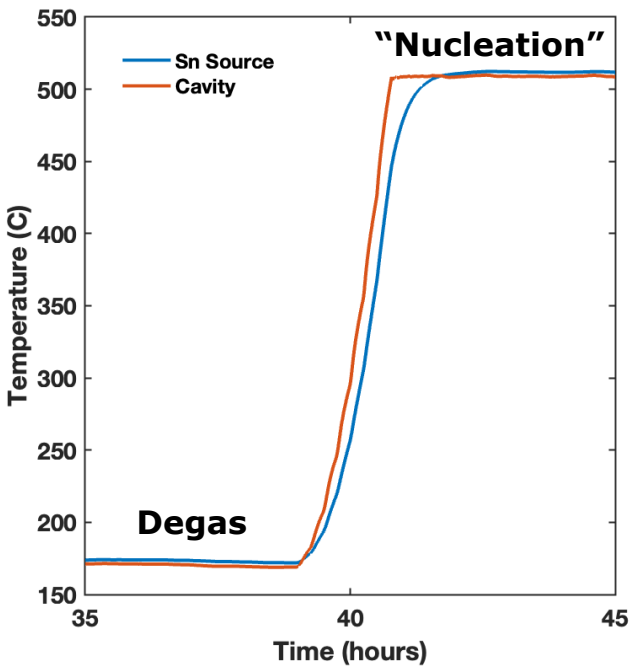
Van Do

Do, Brown, Shpani et al. J. Phys. Chem. C (under review)

Tracking oxide evolution

Samples were annealed in UHV following the vapor diffusion temperature profile ramp to nucleation temperatures

Sample	Ramp rate
C1 (control)	3 C/min
A1 (anodized, porous)	3 C/min
A2 (anodized, porous)	7 C/min



Jasper Brown



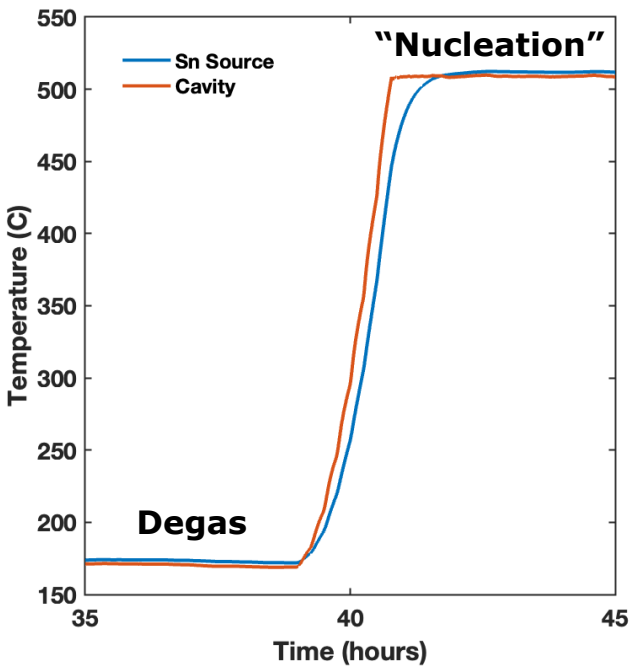
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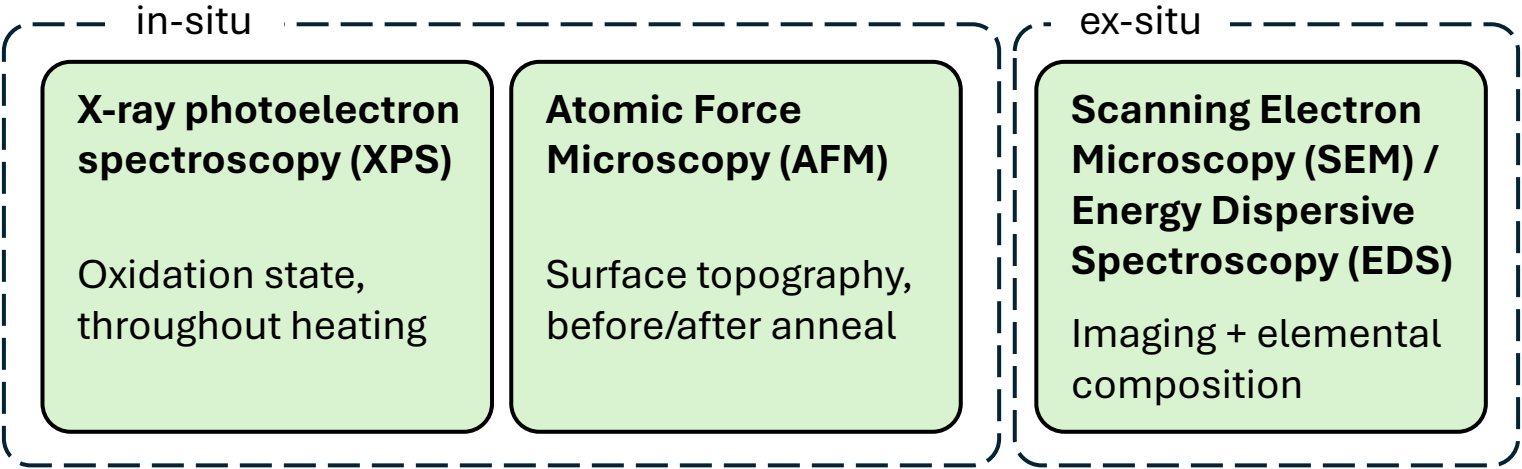
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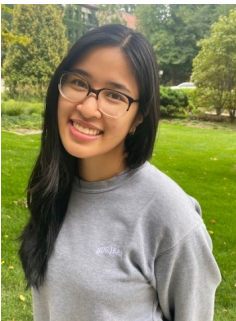
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Characterization Methods



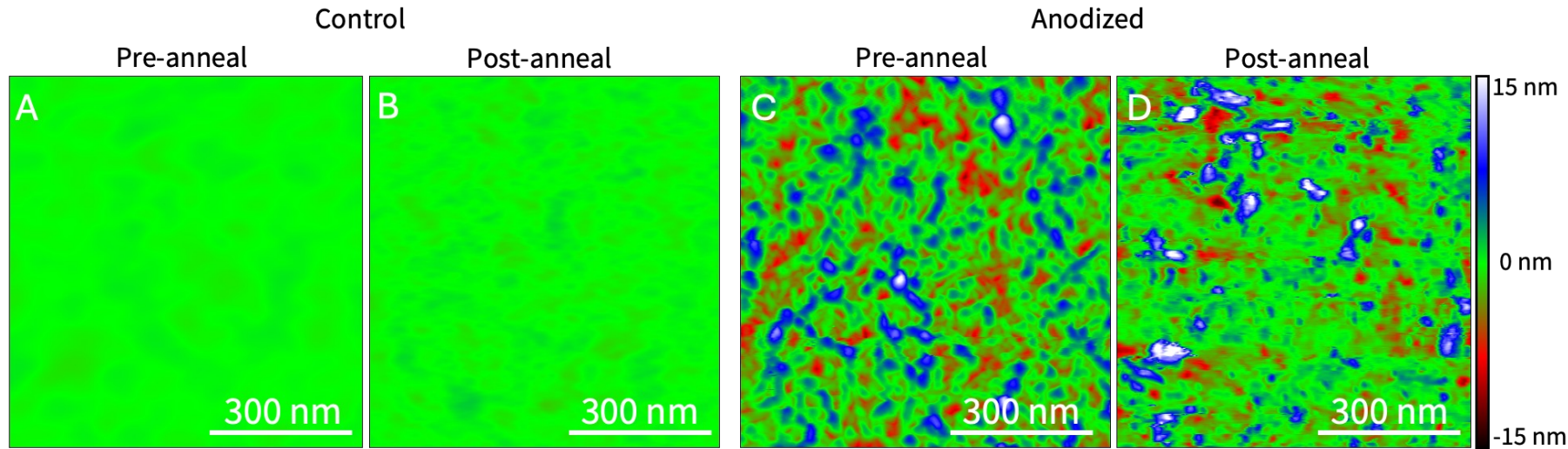
Jasper Brown



Van Do

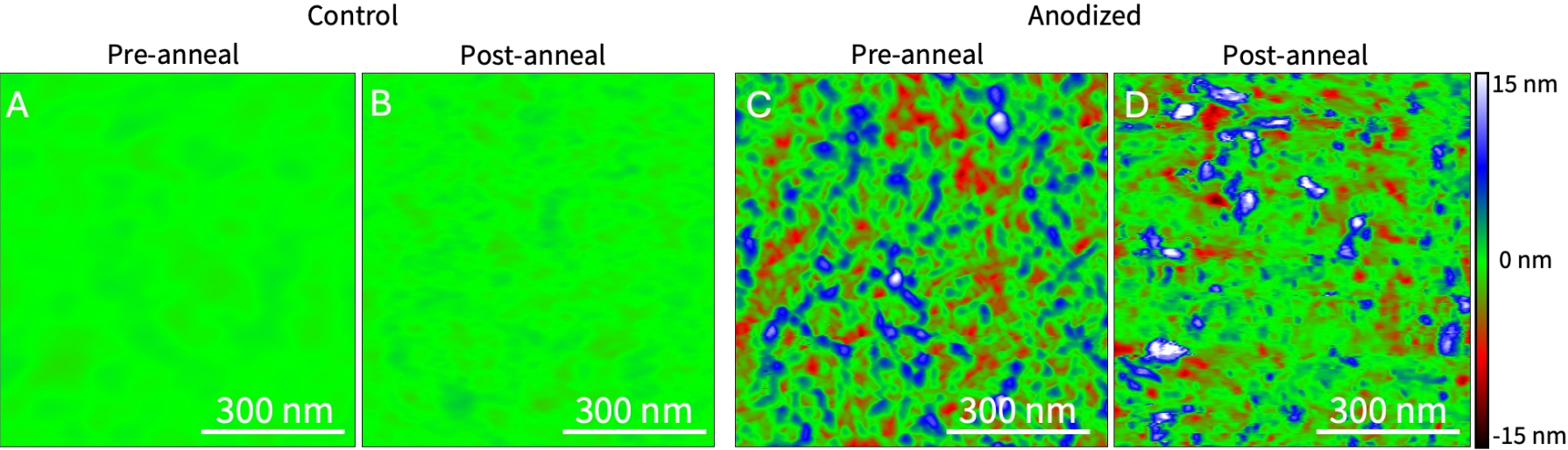
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Porous anodization roughness is irreversible

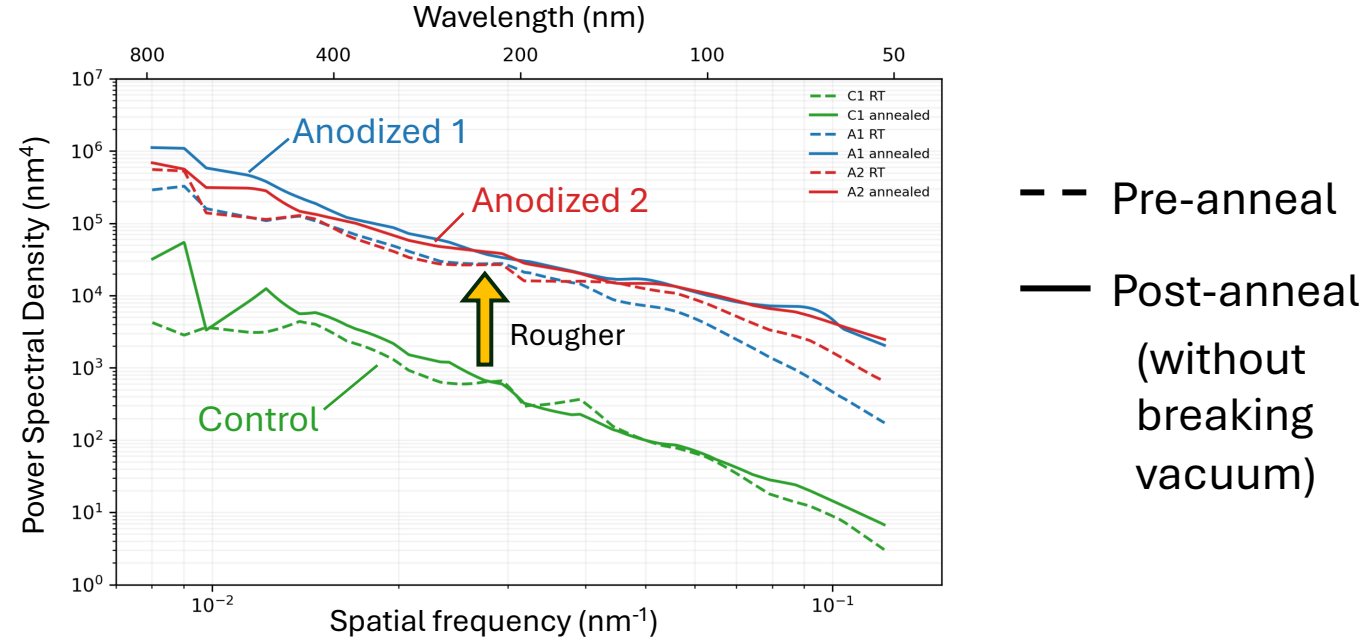


Anodized surface has a rough texture consisting of pores and intersecting bumps, which persist after annealing

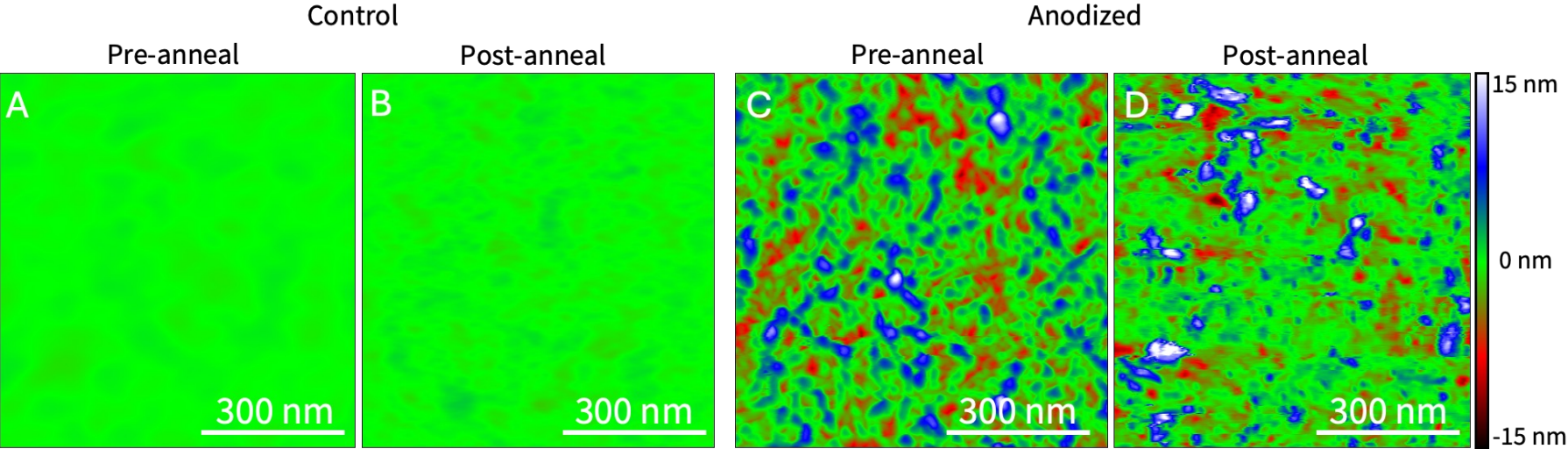
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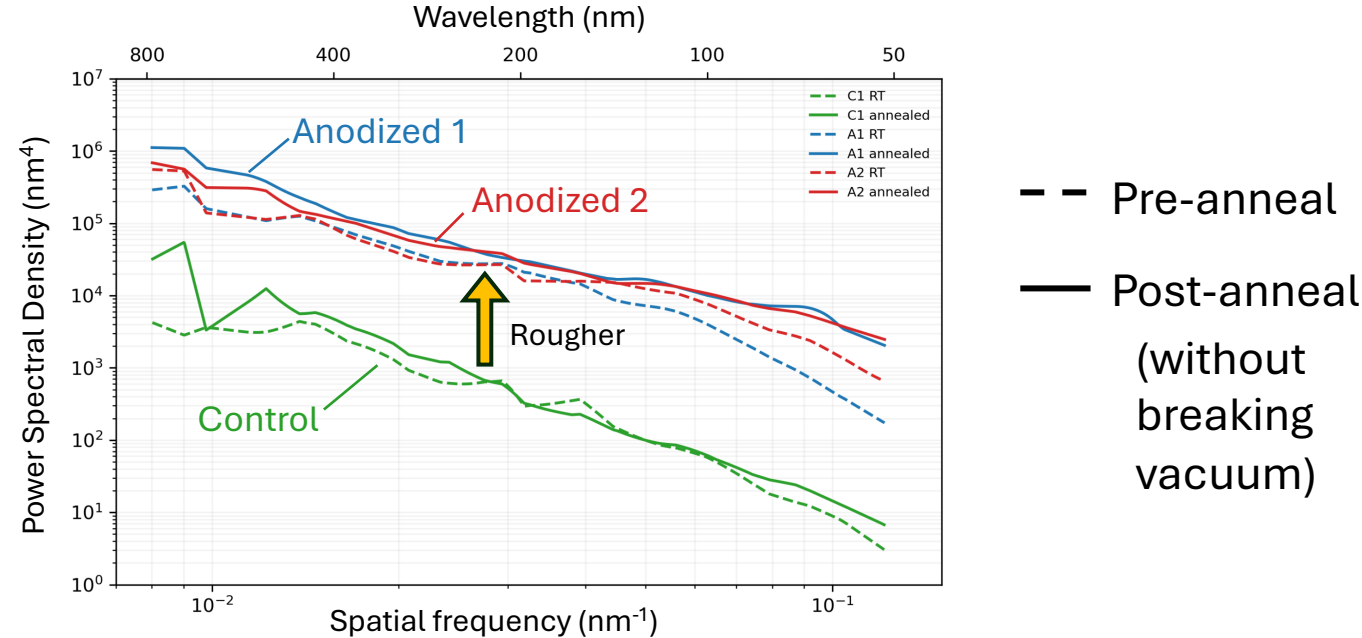
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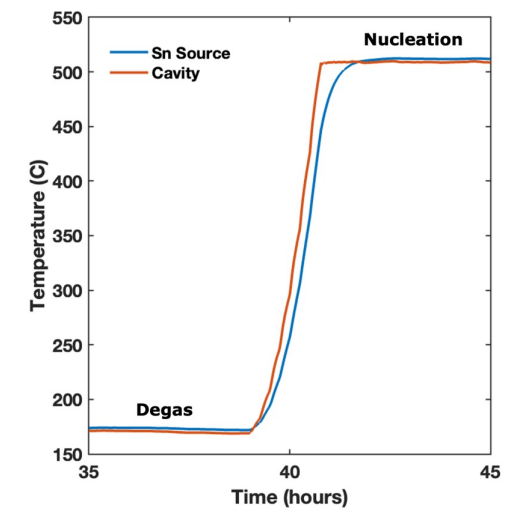
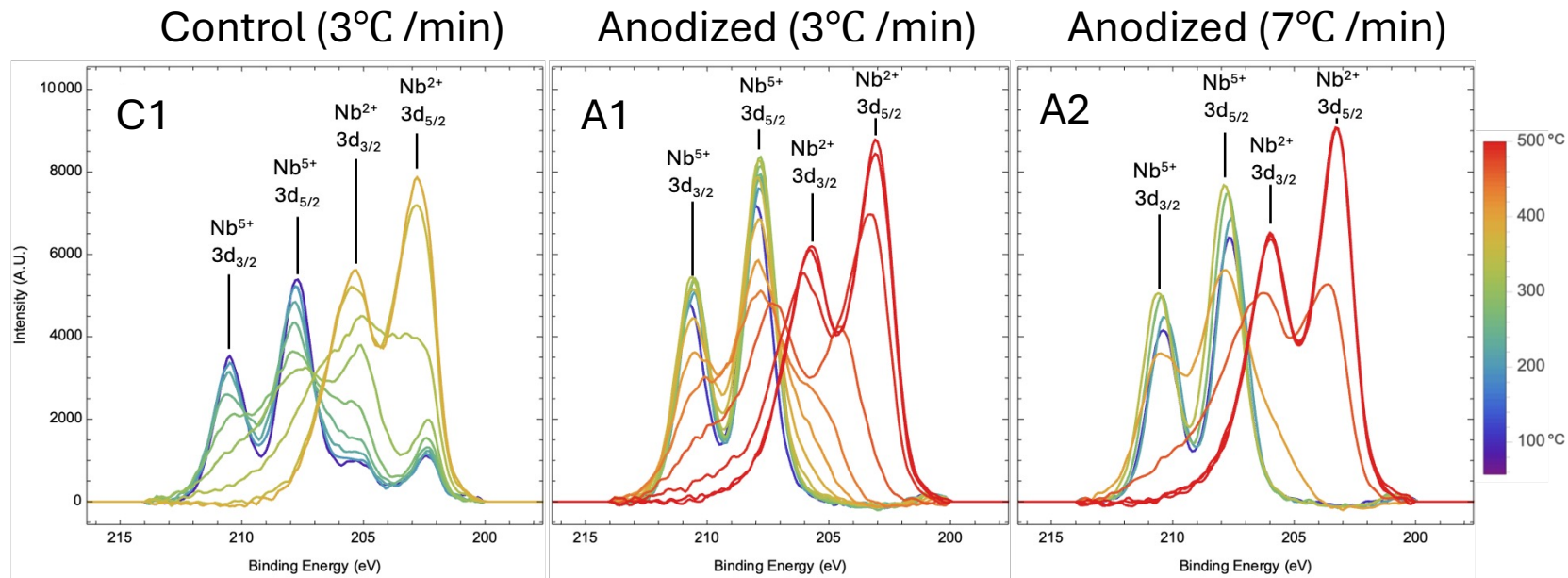


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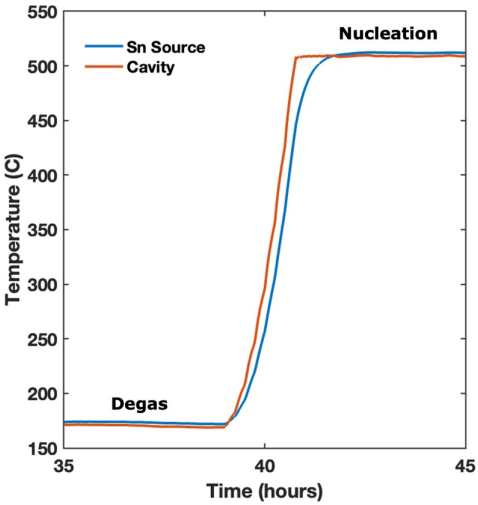
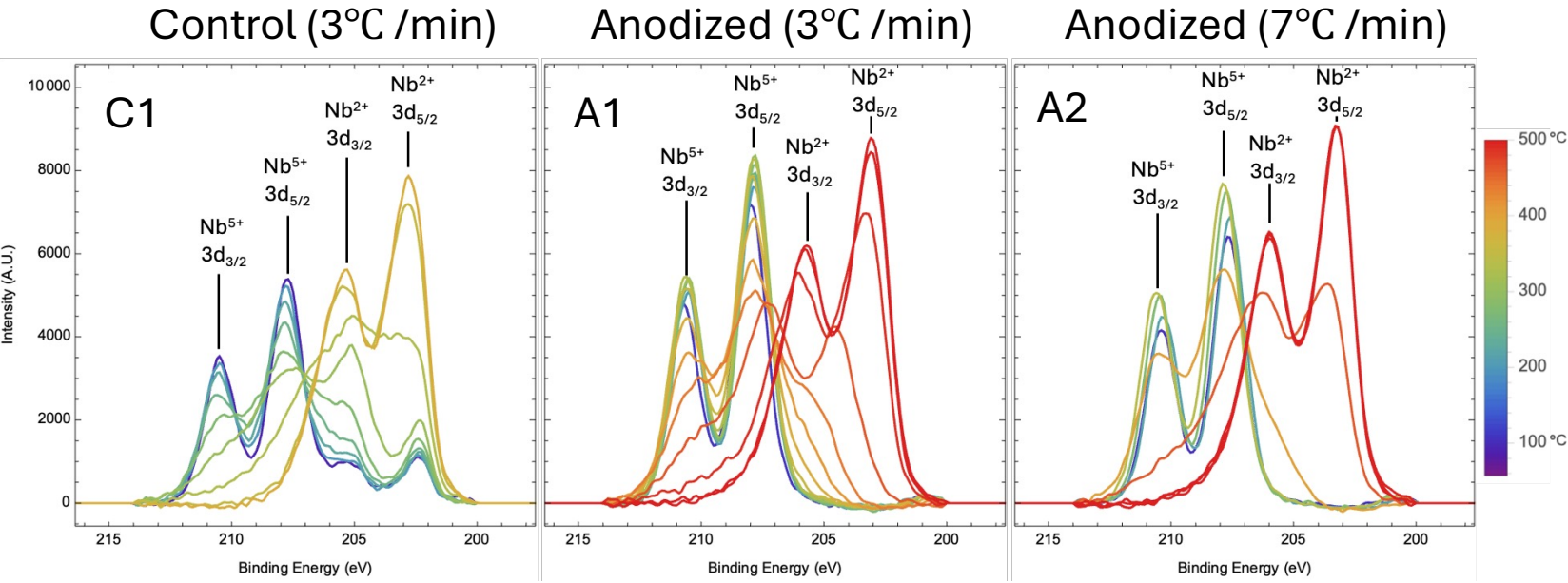


Anodized samples are rougher than control; roughness does not change substantially after UHV annealing

Oxide dissolution kinetics

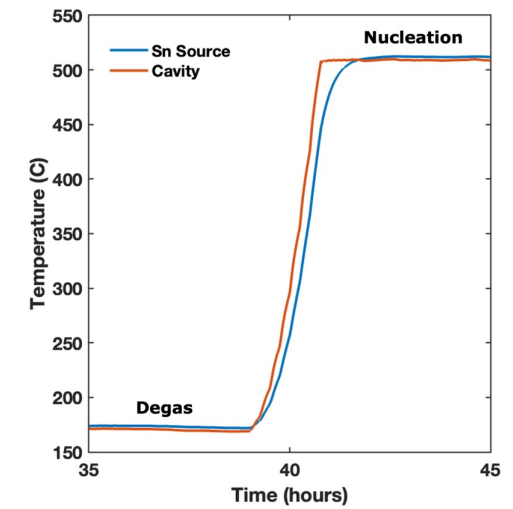
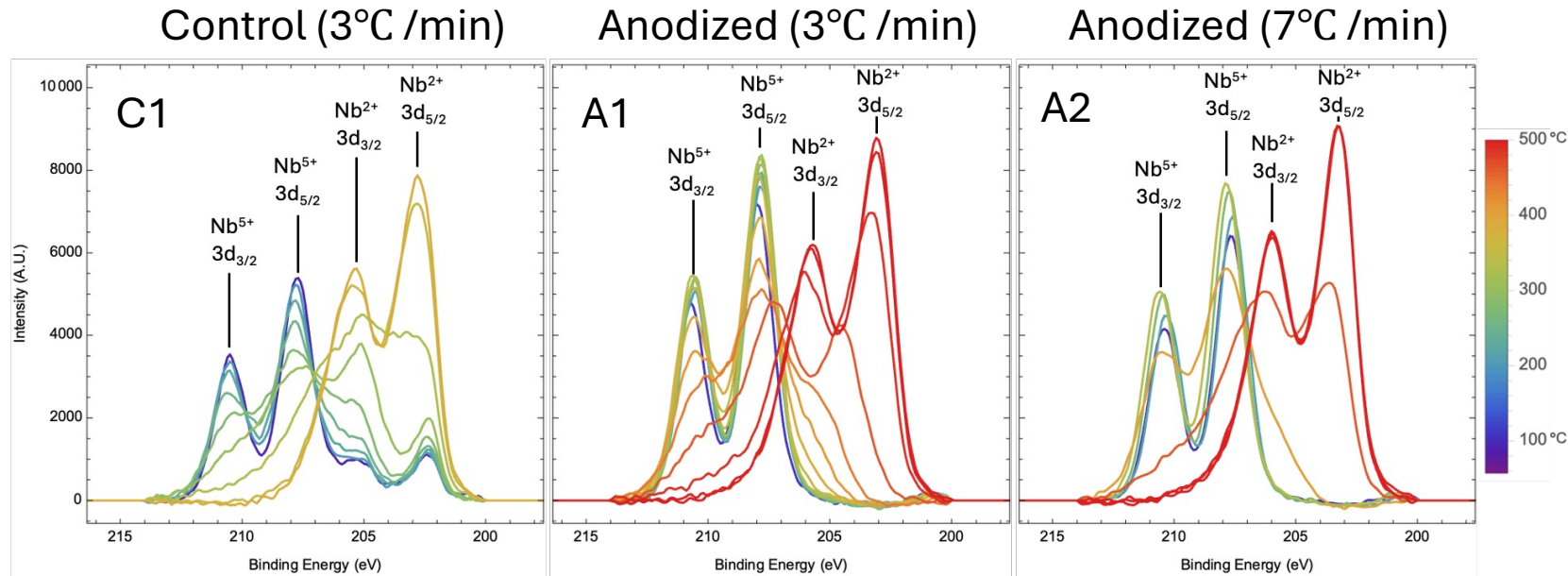


Oxide dissolution kinetics



Nb⁵⁺ peaks disappear at higher temperatures for the anodized samples compared to the control

Oxide dissolution kinetics



Nb^{5+} peaks disappear at higher temperatures for the anodized samples compared to the control

Assuming first-order kinetics, reduction rate follows Arrhenius form:

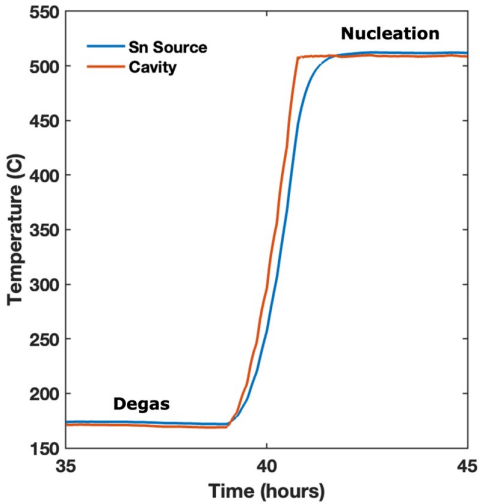
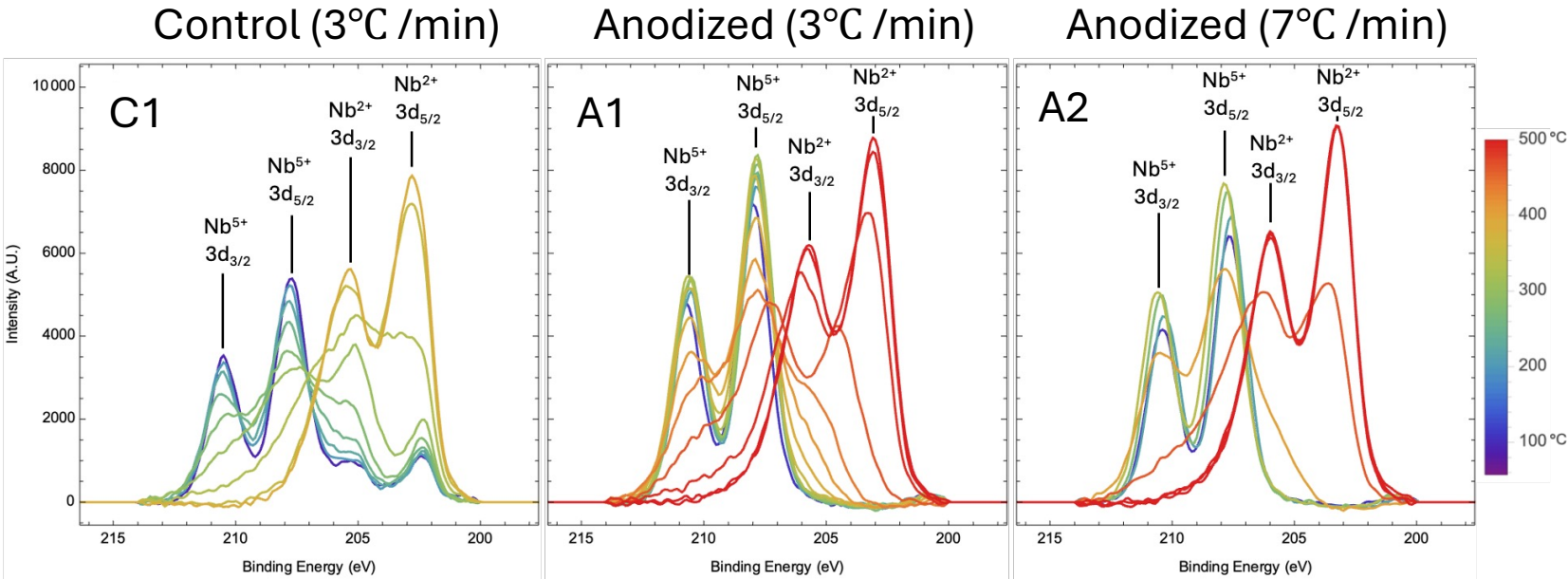
$$\frac{d}{dt} [Nb^{5+}] = -A e^{-\frac{E_a}{RT(t)}} [Nb^{5+}]$$

Activation energy

Frequency factor

Extracted from XPS data

Oxide dissolution kinetics



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Assuming first-order kinetics, reduction rate follows Arrhenius form:

$$\frac{d}{dt} [Nb^{5+}] = -A e^{-\frac{E_a}{RT(t)}} [Nb^{5+}]$$

Frequency factor A (indicated by a red arrow pointing to A)

Activation energy E_a (indicated by a red arrow pointing to E_a)

Extracted from XPS data (indicated by a black arrow pointing to $[Nb^{5+}]$)

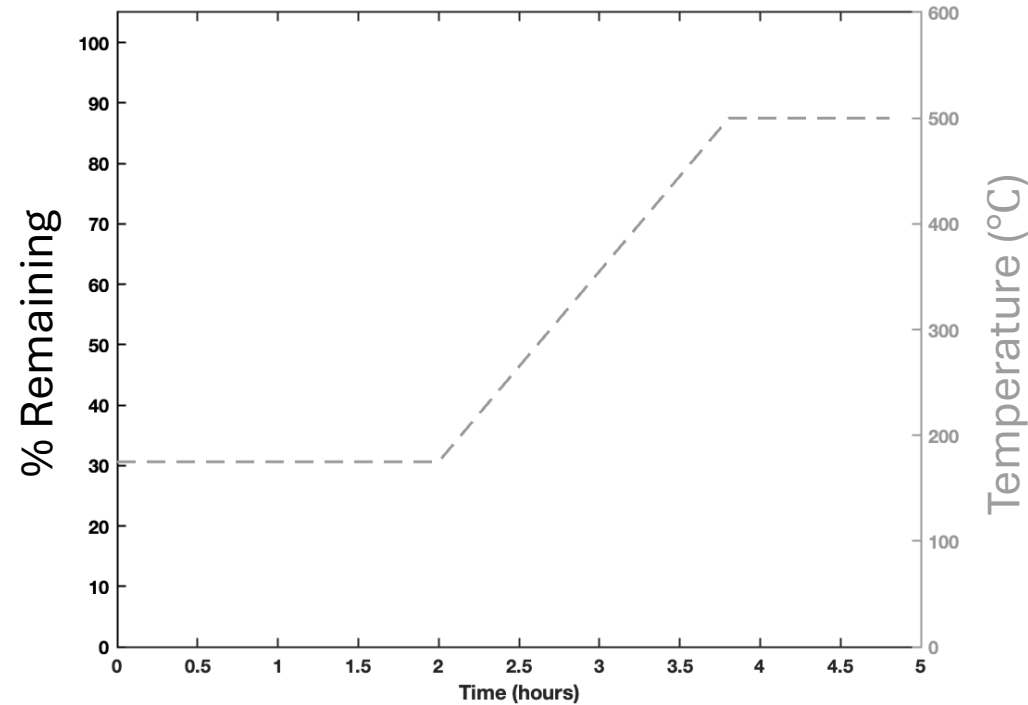
A large blue arrow points from the equation towards the text box on the right.

Use fitted parameters to model thickness of Nb₂O₅ as a function of the temperature profile in the furnace

Modeling what's happening in the furnace

We can use temperature profile as an input to predict % **remaining of Nb₂O₅ layer**:

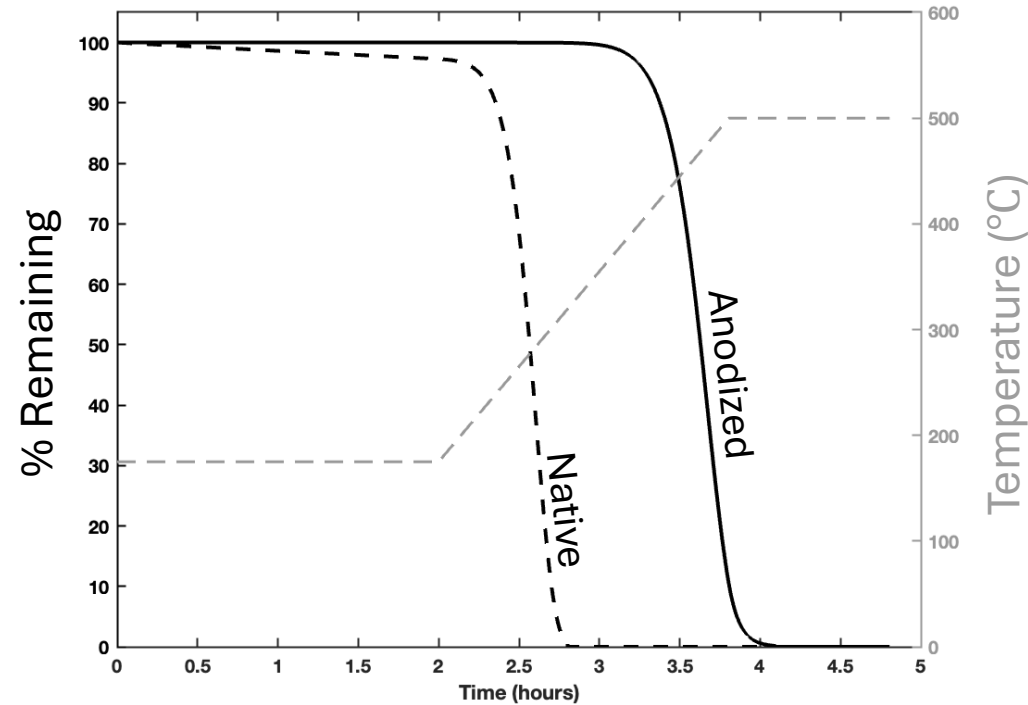
Ramp to nucleation



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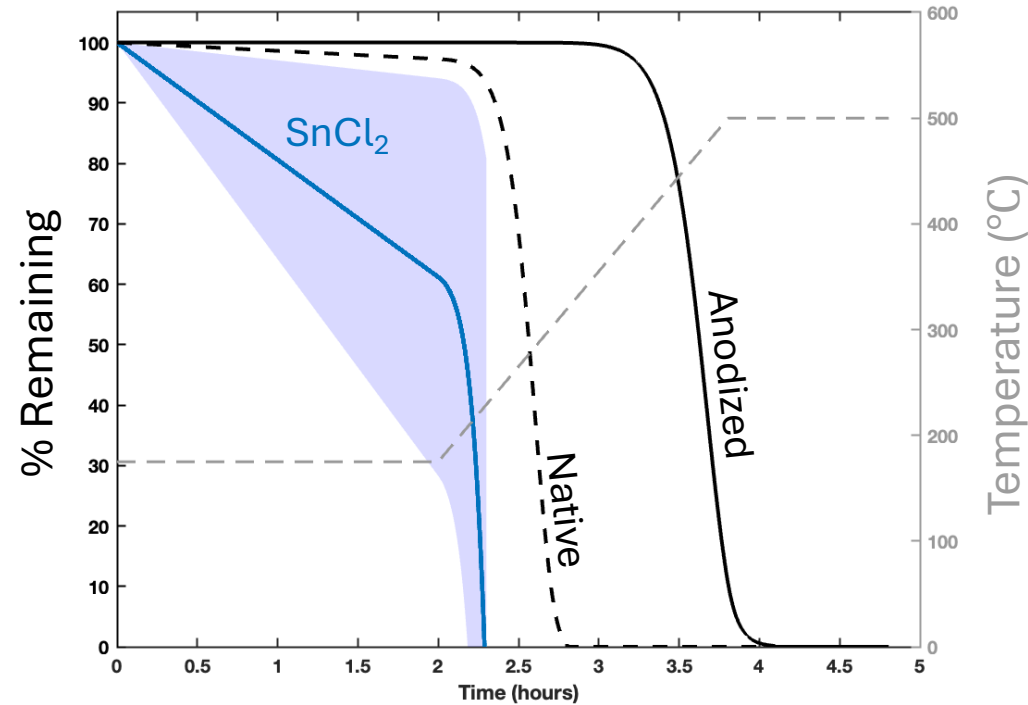
Ramp to nucleation



Modeling what's happening in the furnace

We can use temperature profile as an input to predict % **remaining of Nb_2O_5 layer**, and remaining SnCl_2 in the crucible:

Ramp to nucleation

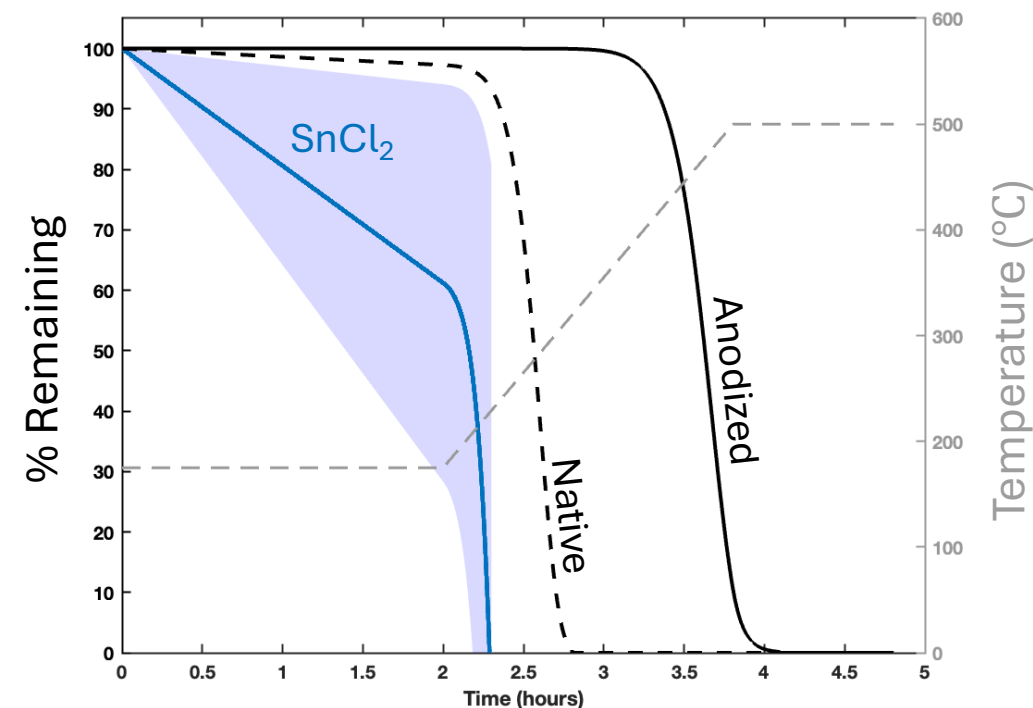


SnCl_2 vapor starts interacting with the Nb_2O_5 surfaces as early as degas

Modeling what's happening in the furnace

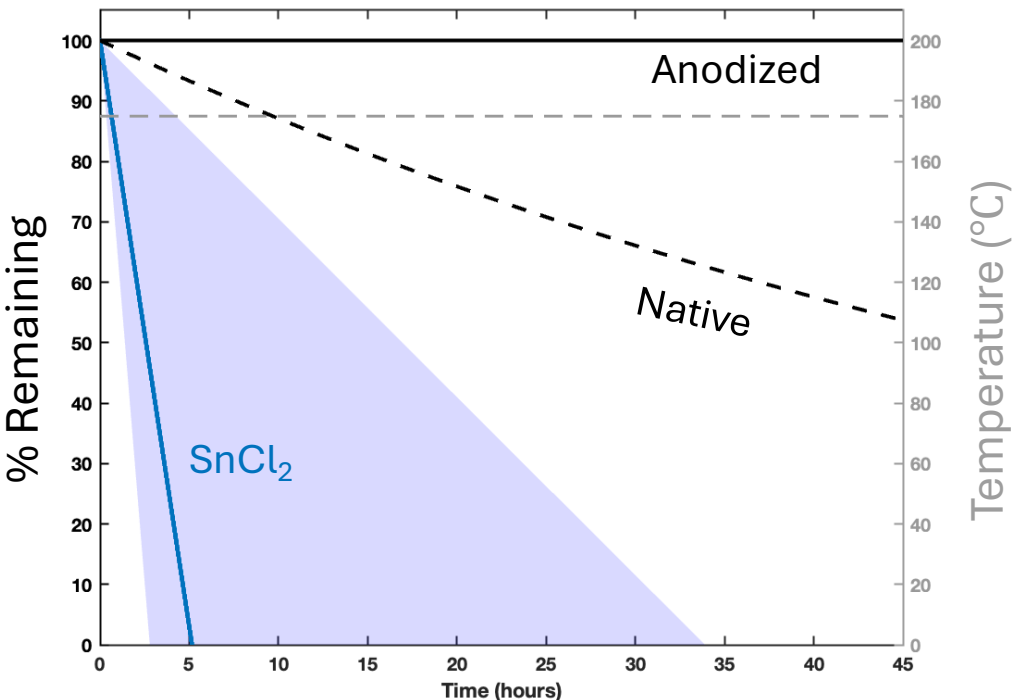
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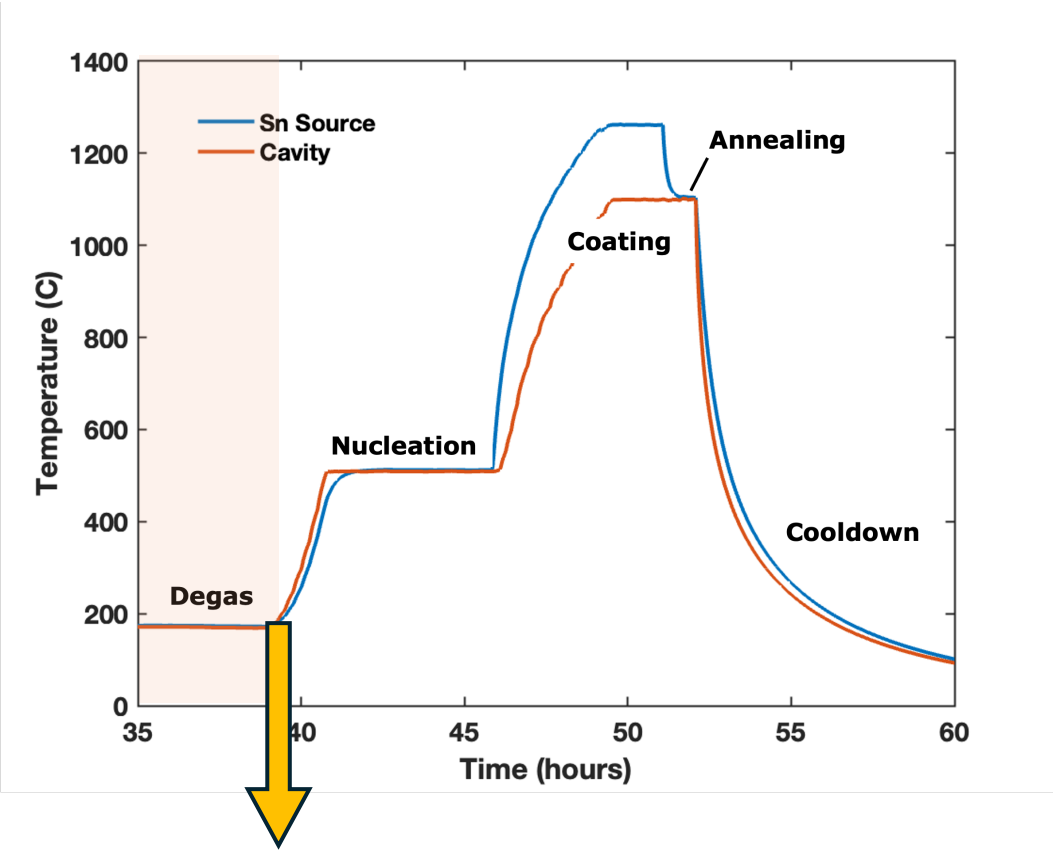
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Degas

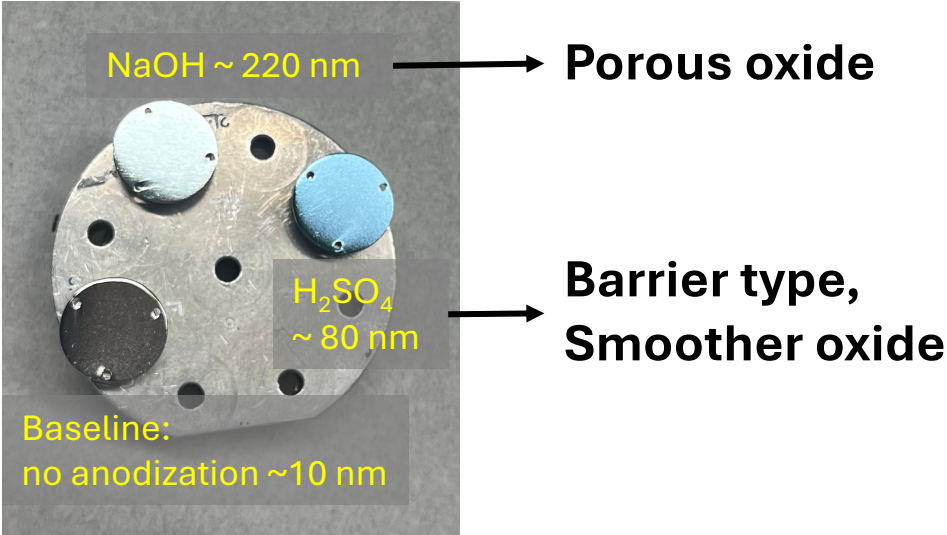


In this example, SnCl_2 vapor is exhausted early in the degas process

Checking experimentally what happens after degas

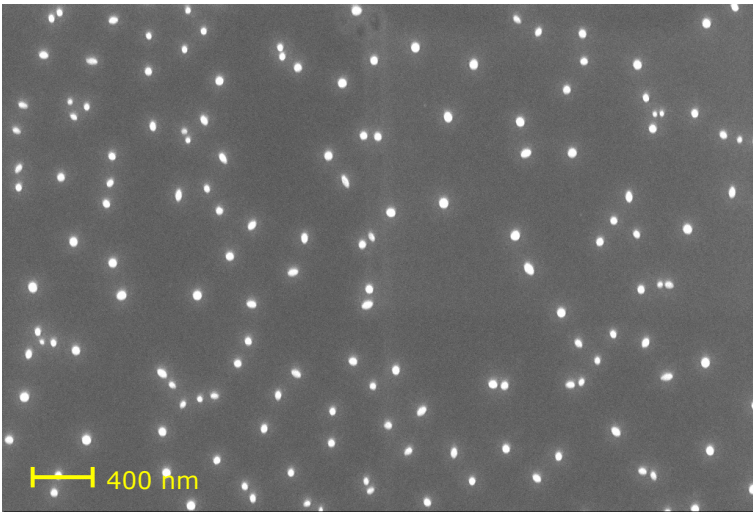
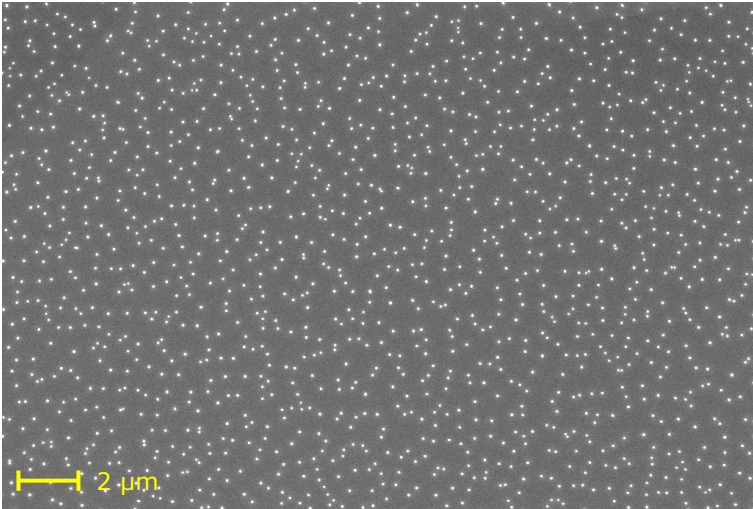


Samples taken out of furnace and underwent surface characterization



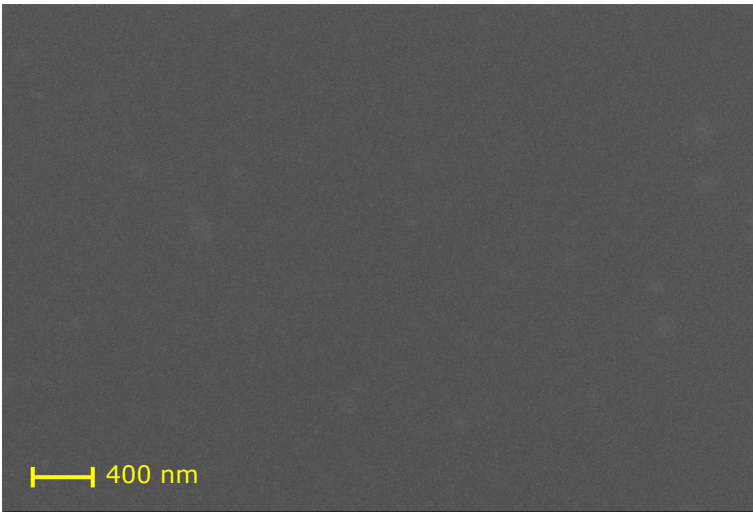
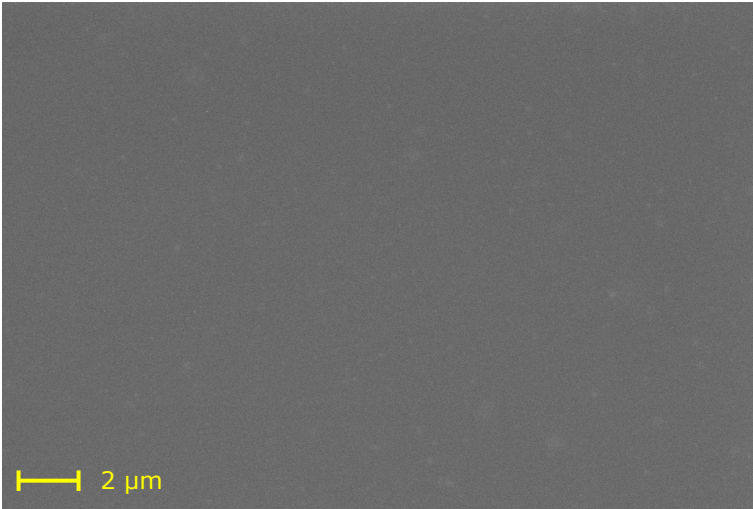
Post 170°C degas with SnCl₂ results

Native Oxide



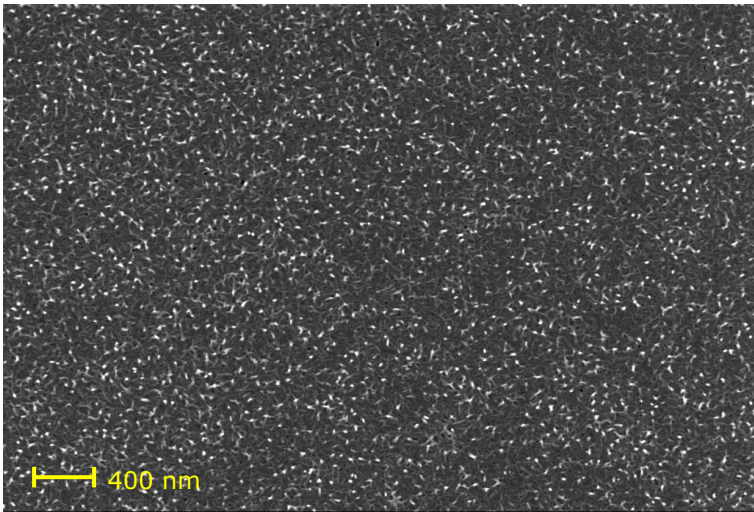
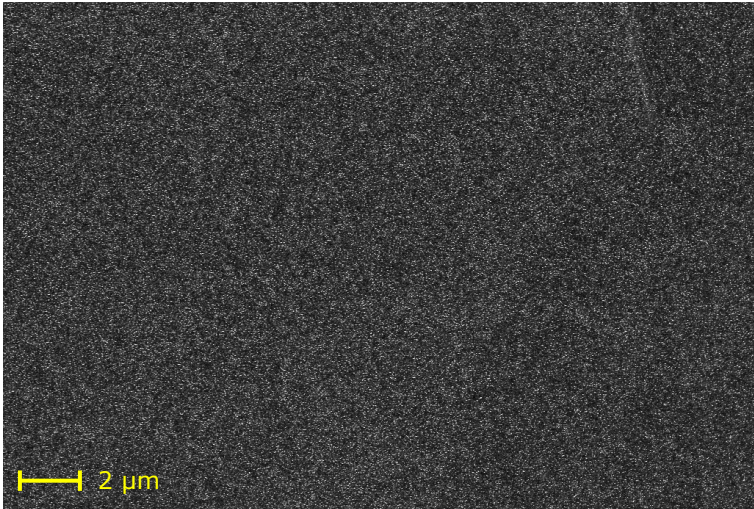
Sn3d/Nb3d (XPS at. %) = 0.25

H₂SO₄ Anodized (Smooth Oxide)



Sn3d/Nb3d (XPS at. %) = 0.38

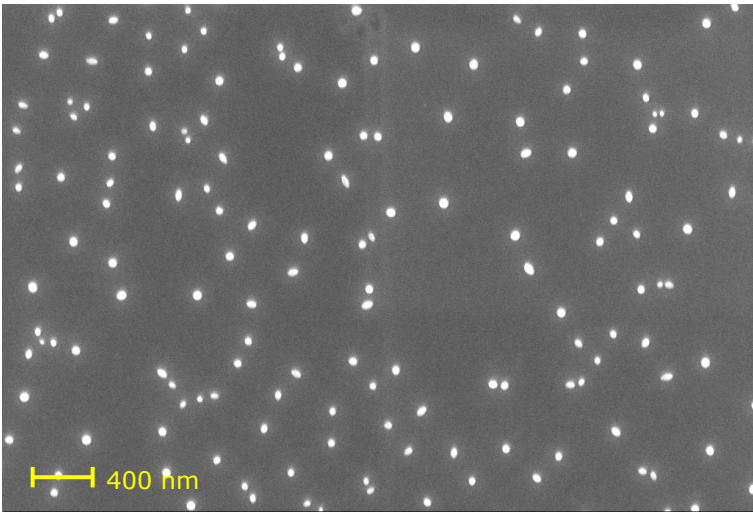
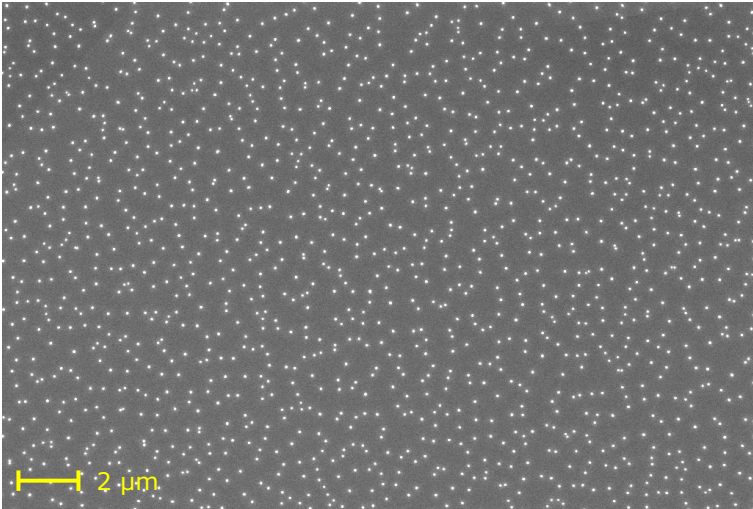
NaOH Anodized (Rough Oxide)



Sn3d/Nb3d (XPS at. %) = 0.89

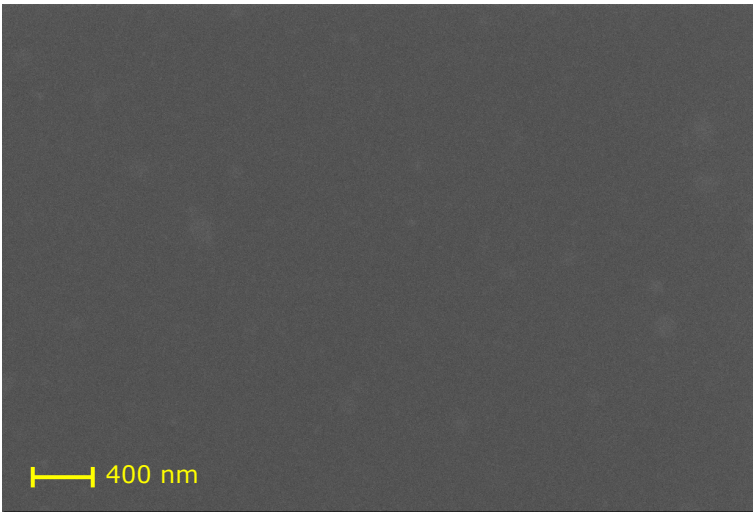
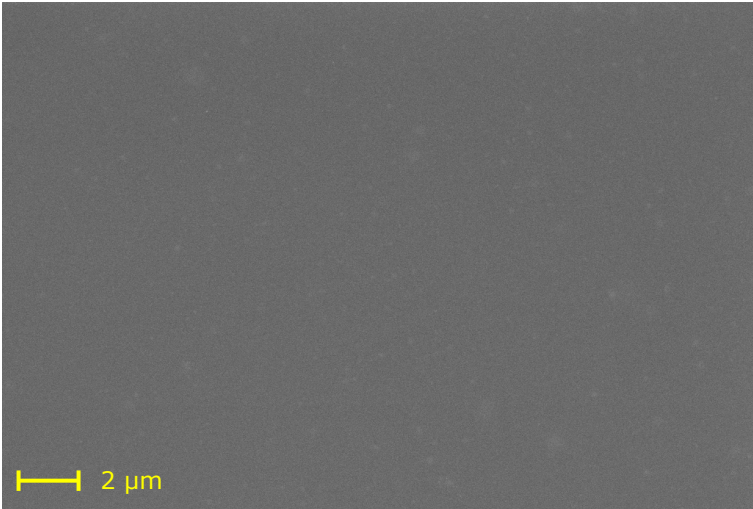
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Native Oxide



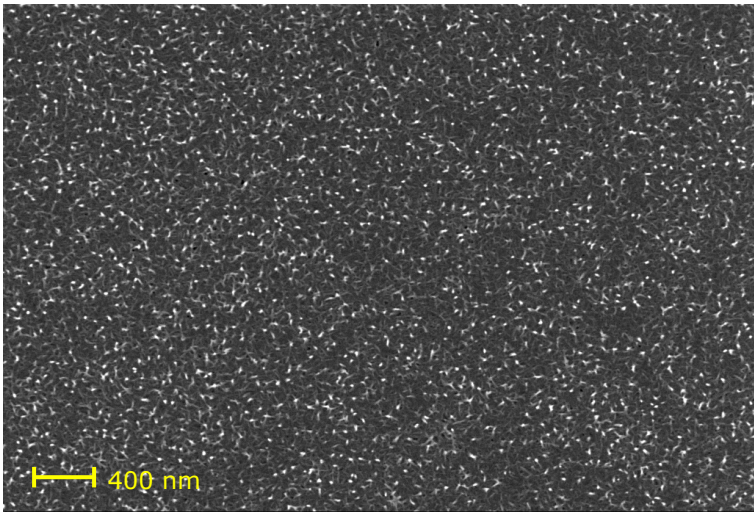
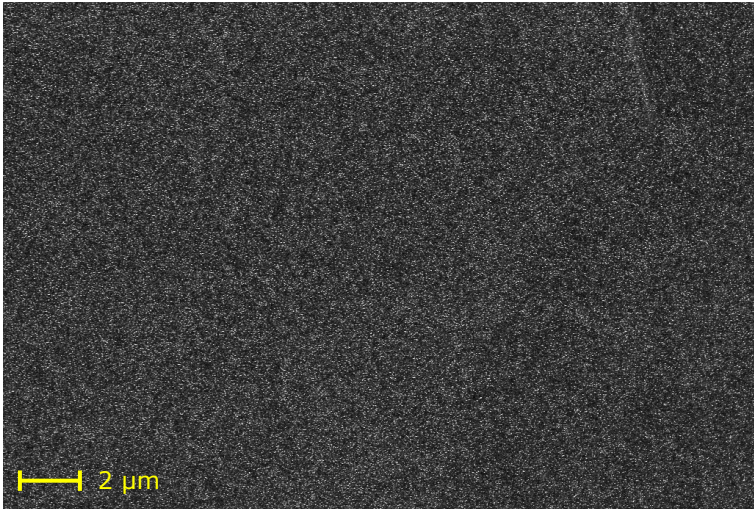
Sn3d/Nb3d (XPS at. %) = 0.25

H₂SO₄ Anodized (Smooth Oxide)



Sn3d/Nb3d (XPS at. %) = 0.38

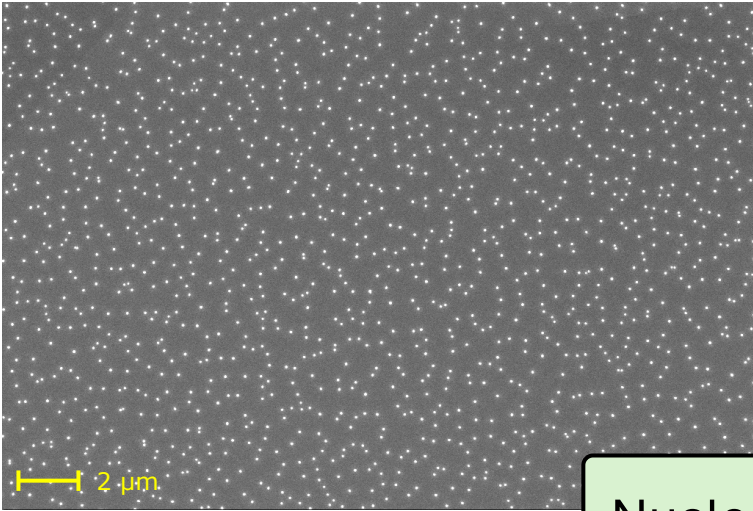
NaOH Anodized (Rough Oxide)



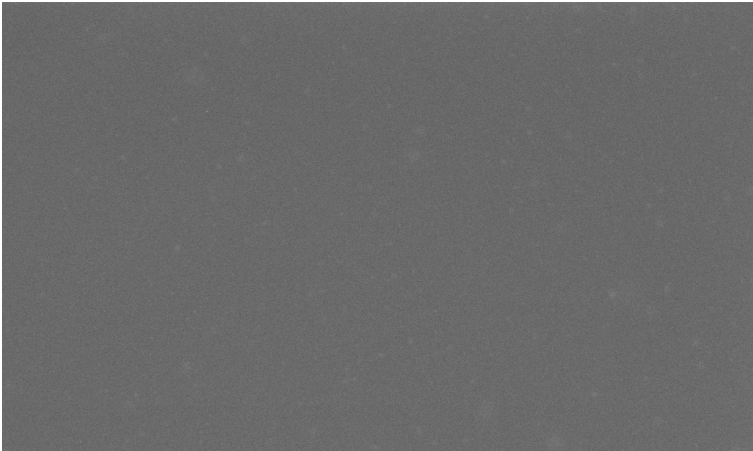
Sn3d/Nb3d (XPS at. %) = 0.89

Post 170°C degas with SnCl₂ results

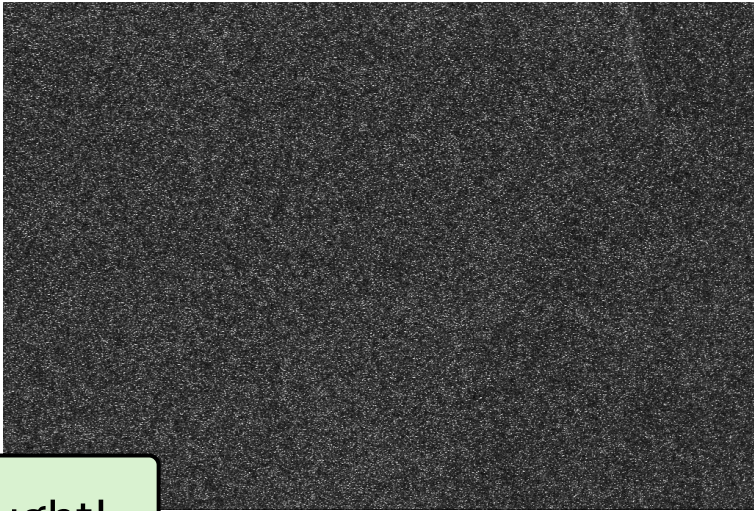
Native Oxide



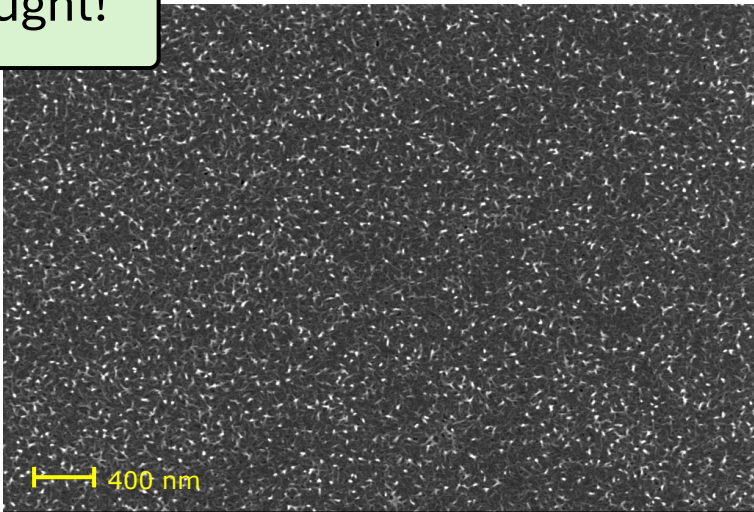
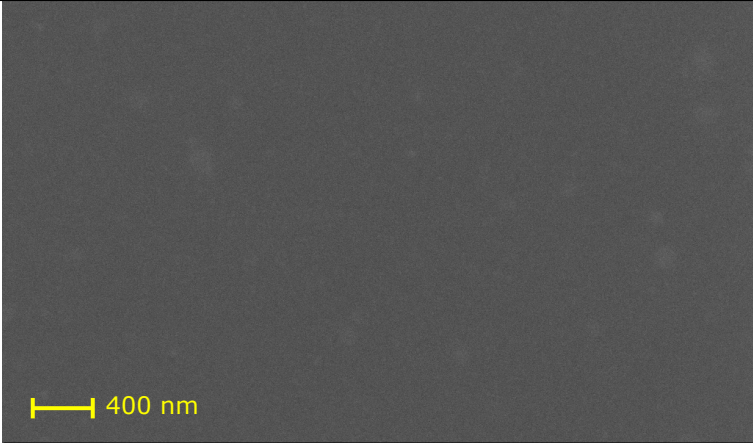
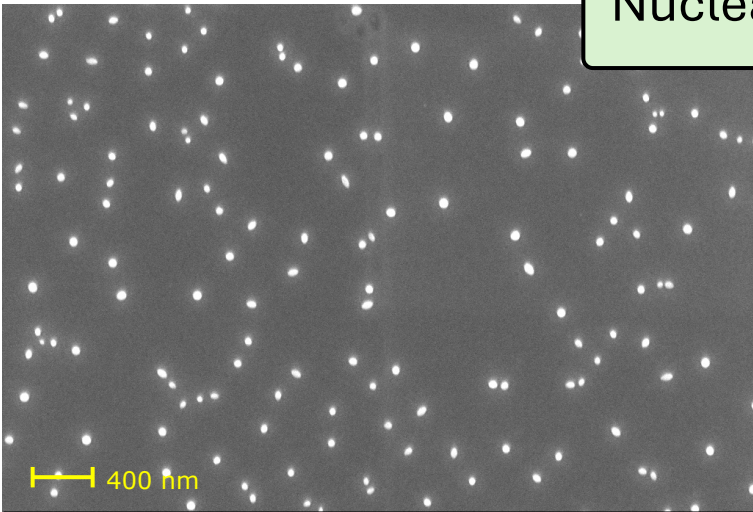
H₂SO₄ Anodized (Smooth Oxide)



NaOH Anodized (Rough Oxide)



Nucleation happens earlier than previously thought!

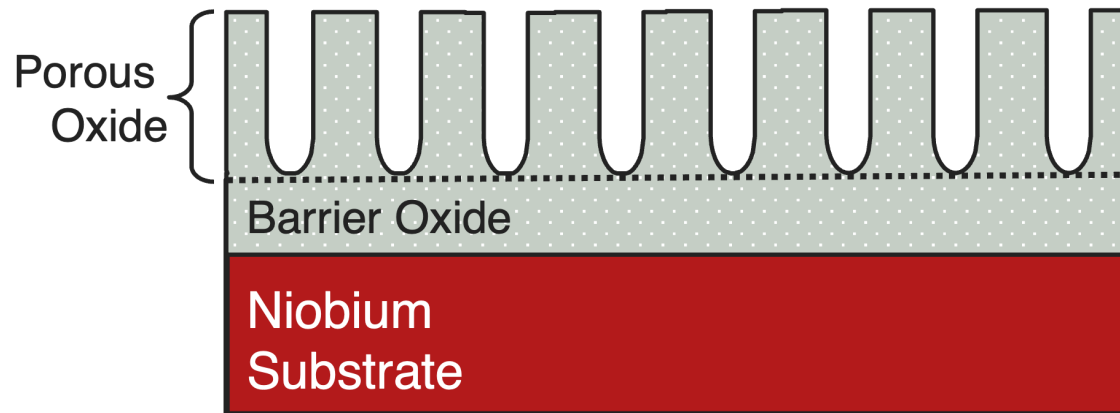


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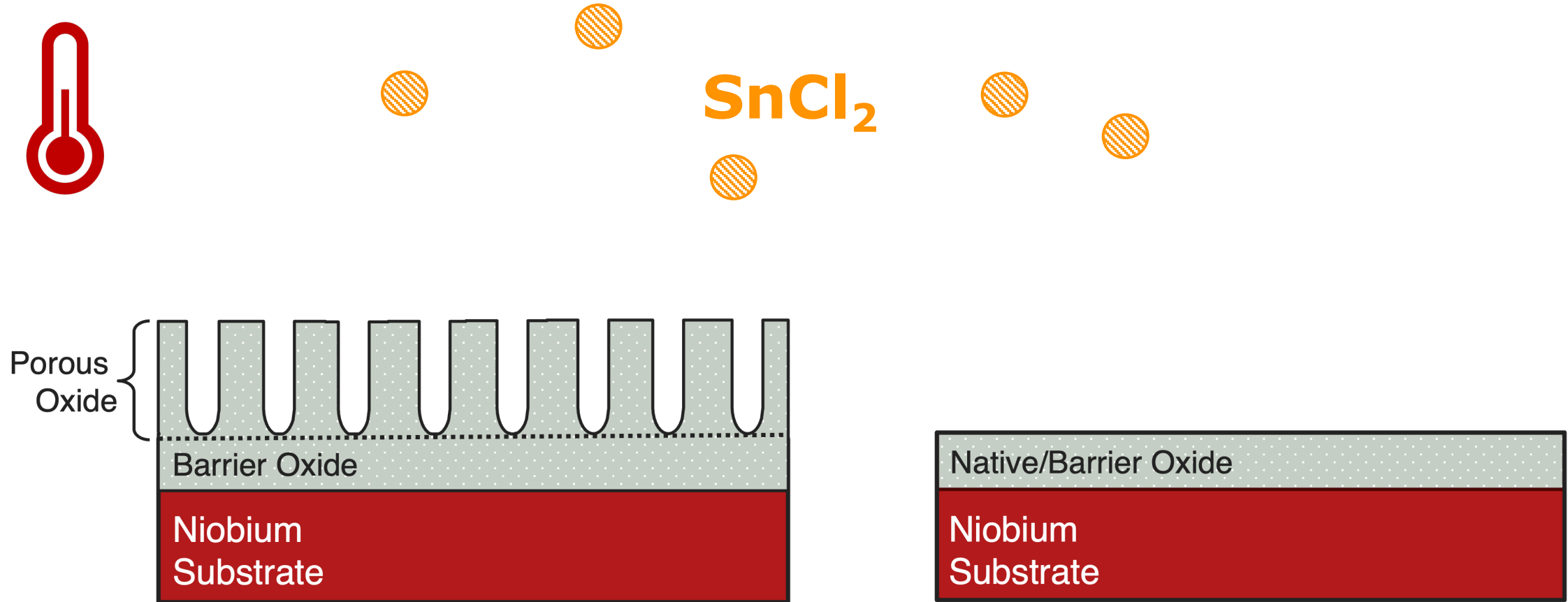
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Sn3d/Nb3d (XPS at. %) = 0.89

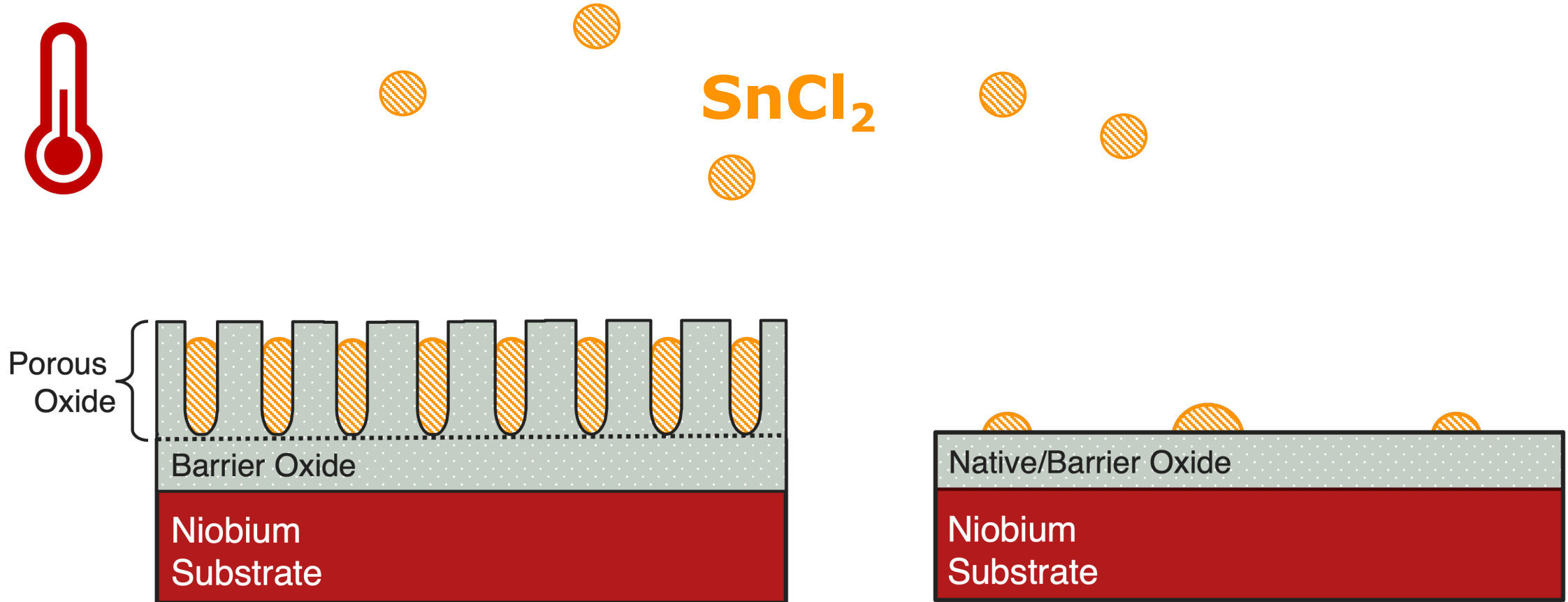
Porous oxide takes in more SnCl_2 : simplified picture



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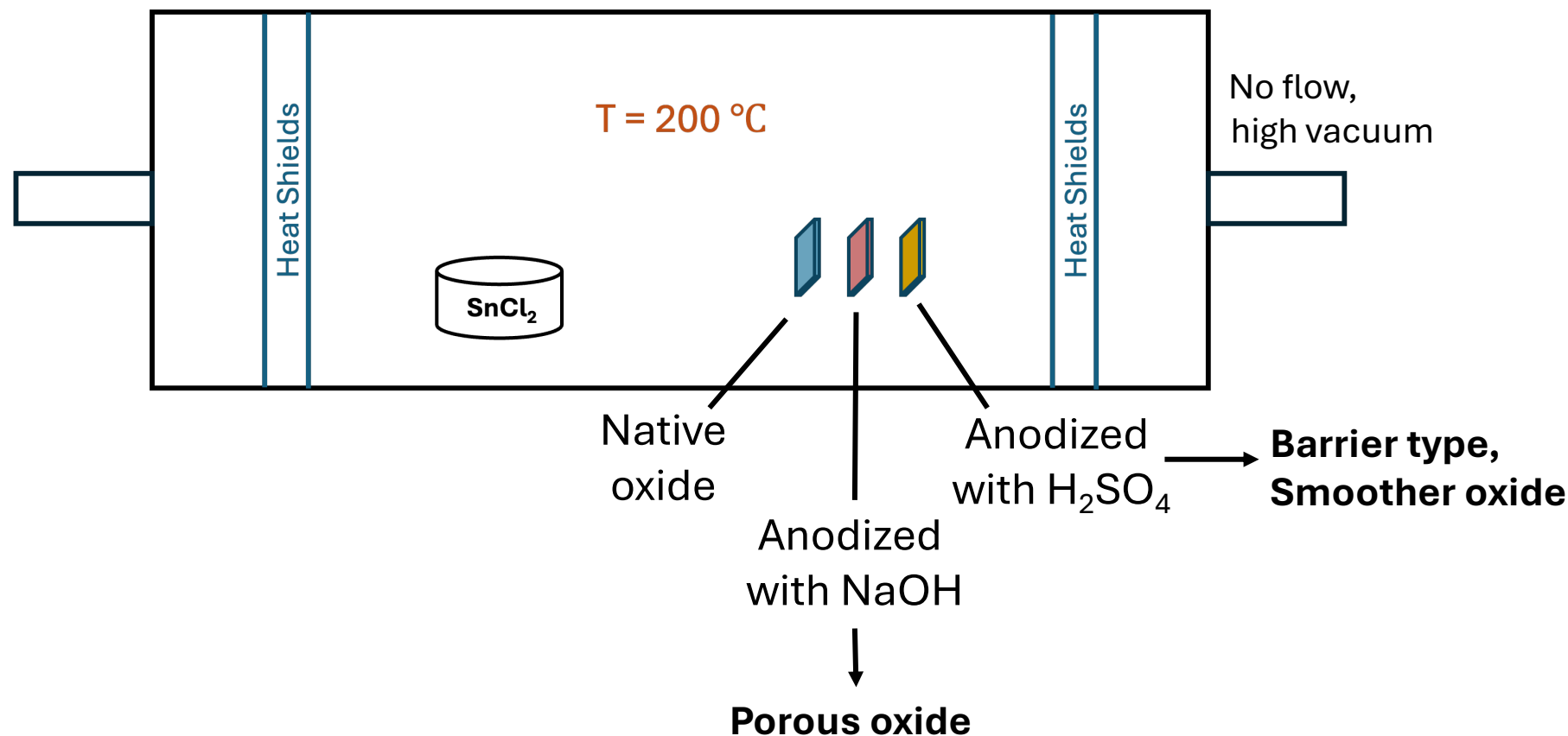


Porous oxide takes in more SnCl_2 : simplified picture



SnCl₂ sublimation study

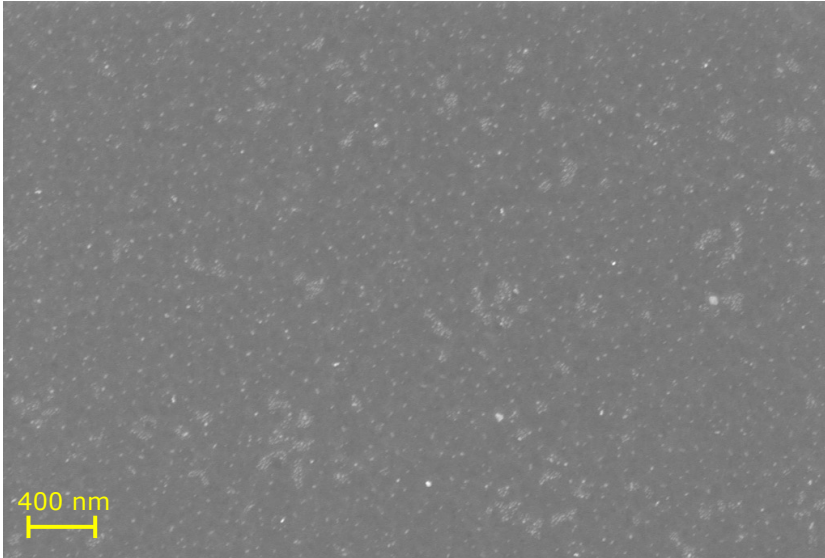
Using the annealing functionality of the Chemical Vapor Deposition (CVD) furnace, we can mimic vapor-diffusion conditions and study SnCl₂-Nb surface interactions



Gabriel Gaitan

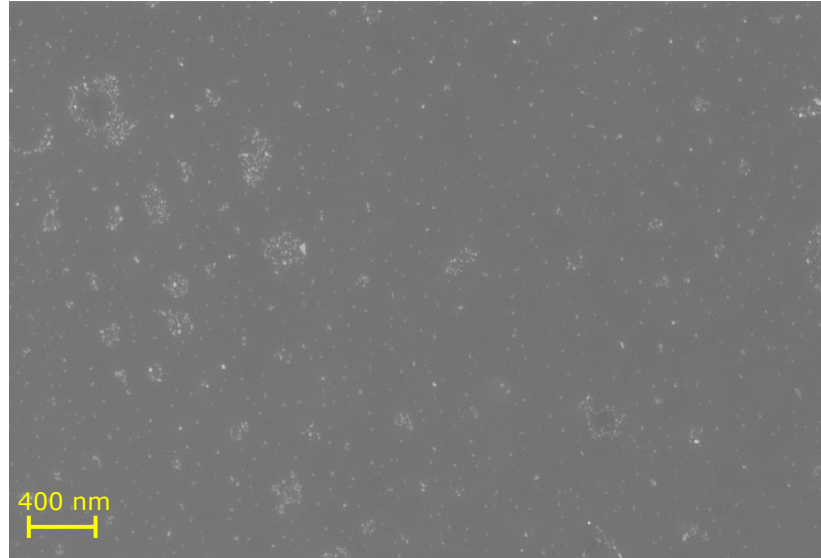
Post 200°C bake with SnCl₂ results

Native Oxide



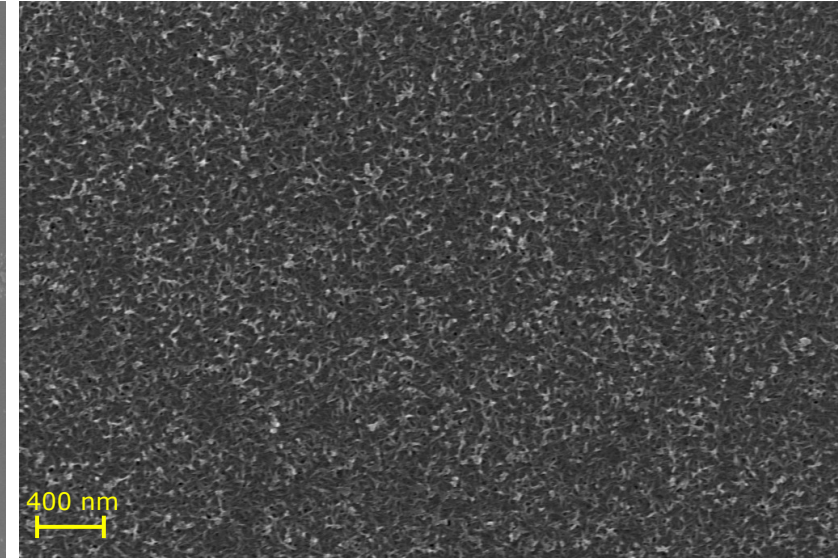
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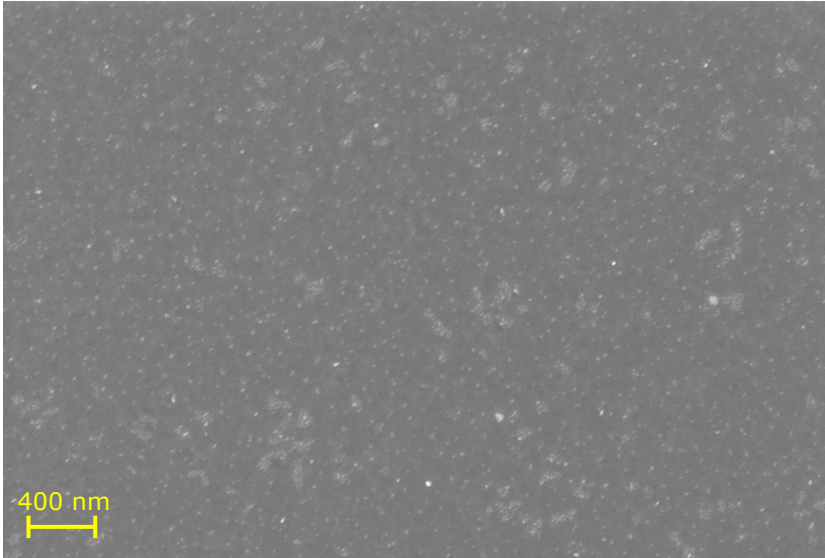


Sn3d/Nb3d (XPS at. %) = 0.93

Same effect was observed: porous oxide has most Sn content

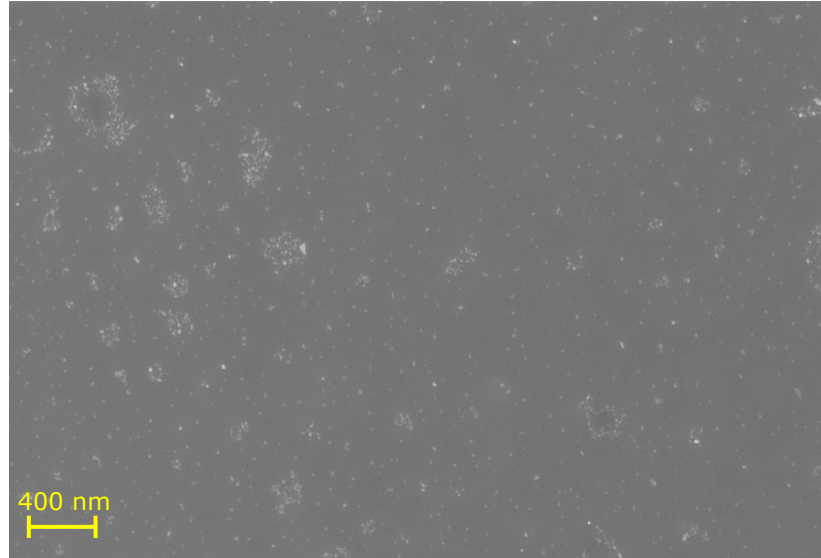
Post 200°C bake with SnCl_2 results

Native Oxide



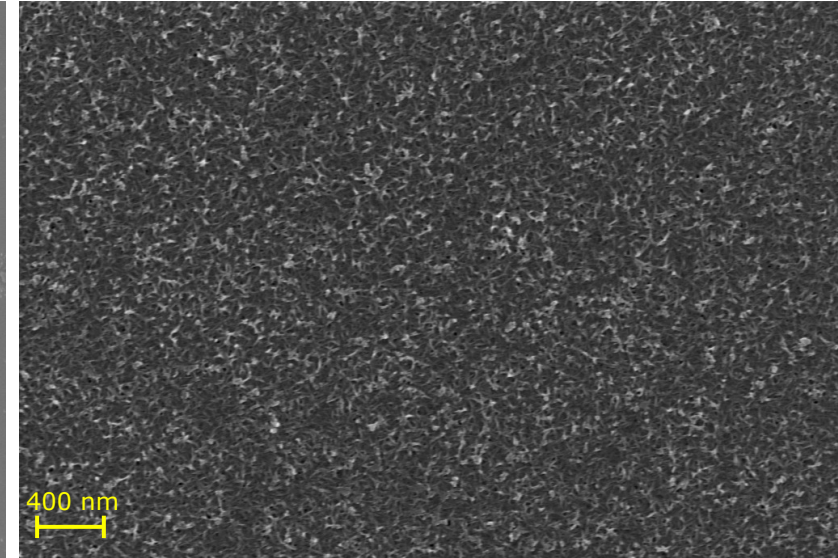
Sn3d/Nb3d (XPS at. %) = 0.24

H_2SO_4 Anodized (Smooth Oxide)



Sn3d/Nb3d (XPS at. %) = 0.38

NaOH Anodized (Rough Oxide)



Sn3d/Nb3d (XPS at. %) = 0.93

Same effect was observed: porous oxide has most Sn content

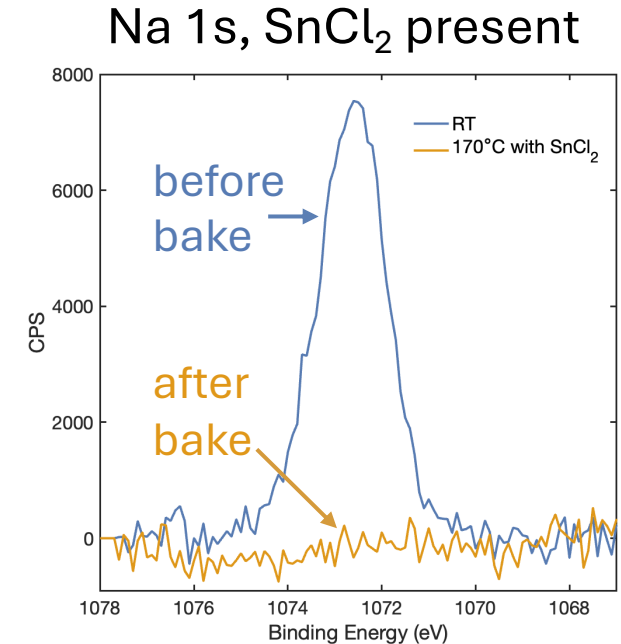
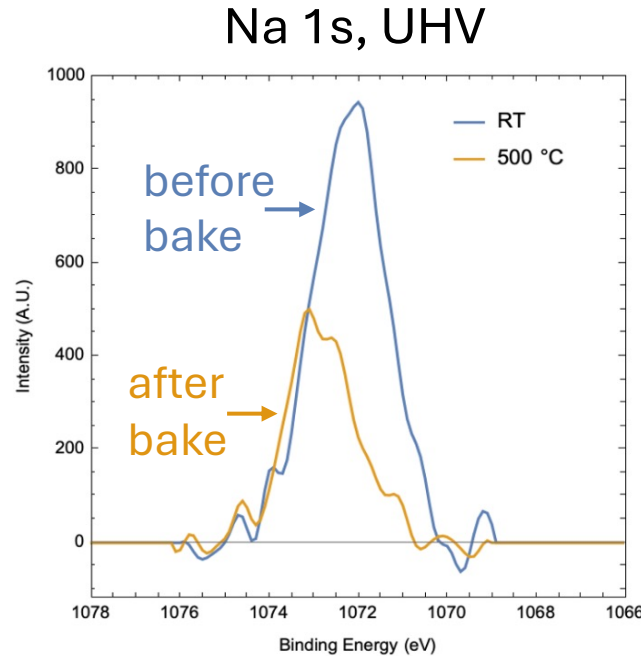
Challenge we faced with multiple runs: degradation of SnCl_2 (lower sublimation rates) due to handling in atmosphere

Some more observations

Surface chemistry reveals Na in porous oxide



Electrolyte incorporation in the oxide during anodization



Na persists after annealing in UHV; however, it goes away when SnCl₂ is present in the chamber!

Takeaways and outlook

Surface roughness persists after oxide reduction through annealing:

→ helpful to separate chemical vs roughness effects in future nucleation studies (using the Chemical Vapor Deposition furnace)

SnCl₂ interacts with the Nb surface earlier than previously assumed (as early as degas stage):

→ important for understanding what actually drives nucleation

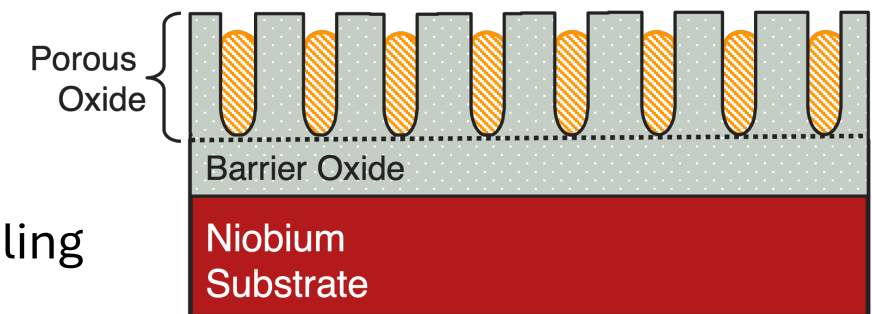
Porous/rough oxides show potential for improved nucleation: no droplets but more tin

→ promising direction to engineer the substrate surface for better (thinner, more uniform) final films

Some things to keep in mind moving forward:

→ Na incorporation in porous oxide surface: does it play a role?

→ SnCl₂ degradation: important consideration for storage and handling



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Thank you for
your attention!

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